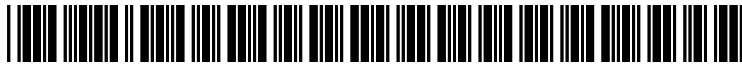

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(54) **TRAY AND SUBSTRATE FIXING DEVICE**

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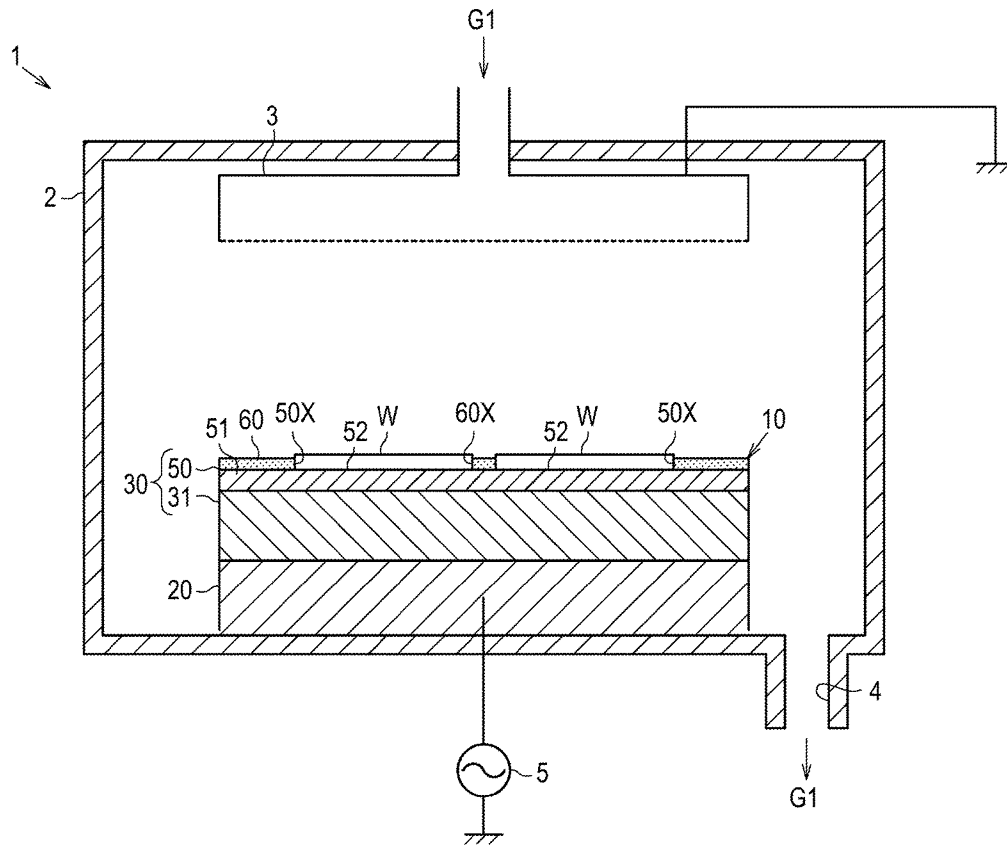
(57) **ABSTRACT**

A tray mounted on an electrostatic chuck includes an accommodation recess configured to accommodate a substrate, a bottom plate portion placed on the electrostatic chuck, a coating film layer made of a material different from the bottom plate portion and formed on an upper surface of the bottom plate portion, and an opening portion penetrating the coating film layer in a thickness direction. The accommodation recess includes an inner side surface of the opening portion and an upper surface of the bottom plate portion exposed from the opening portion. The coating film layer has a multilayer structure including a first coating film having higher plasma resistance than the bottom plate portion and a second coating film laminated on an upper surface of the first coating film and having higher plasma resistance than the first coating film. The first coating film is thicker than the second coating film.

FIG. 1



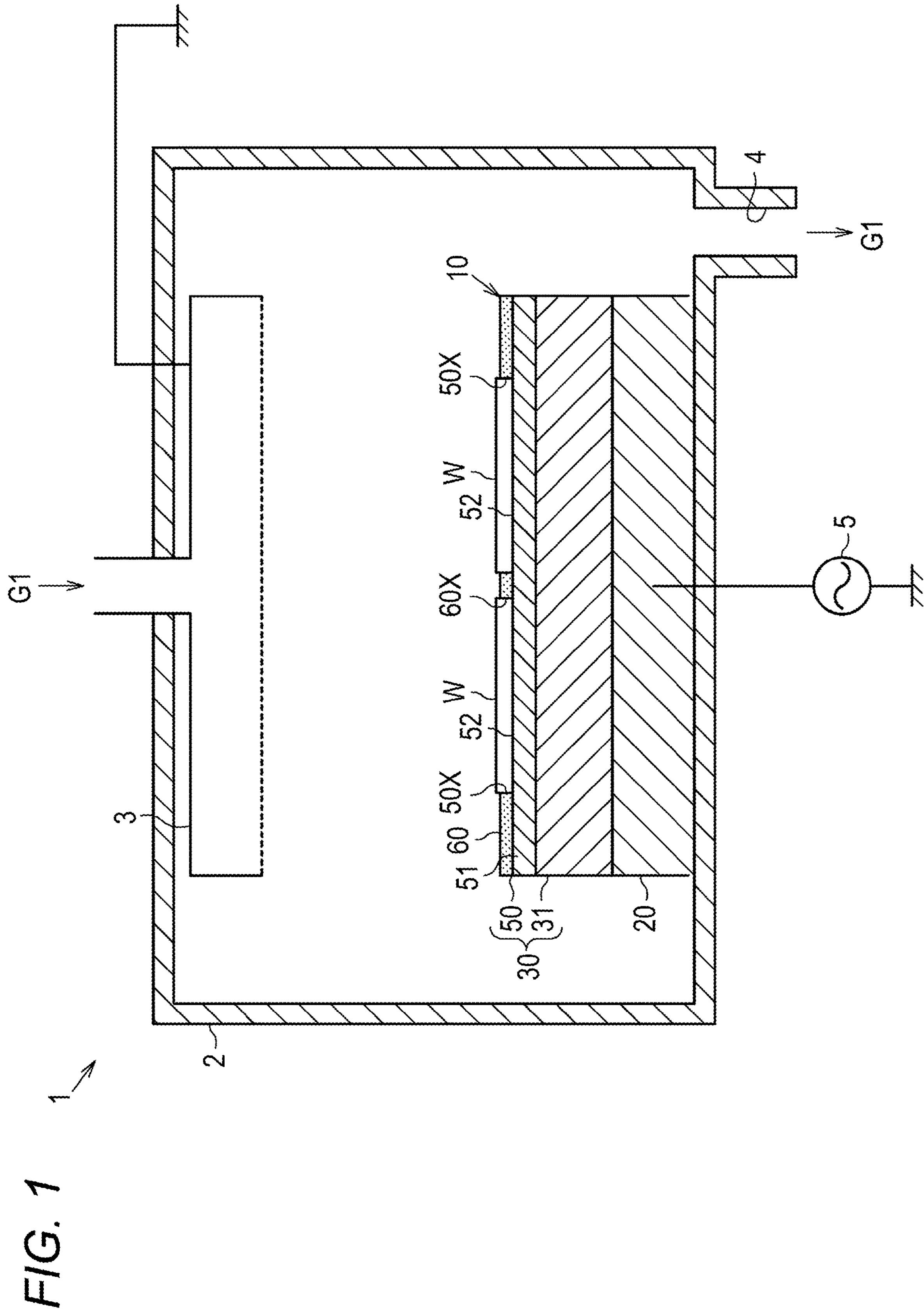
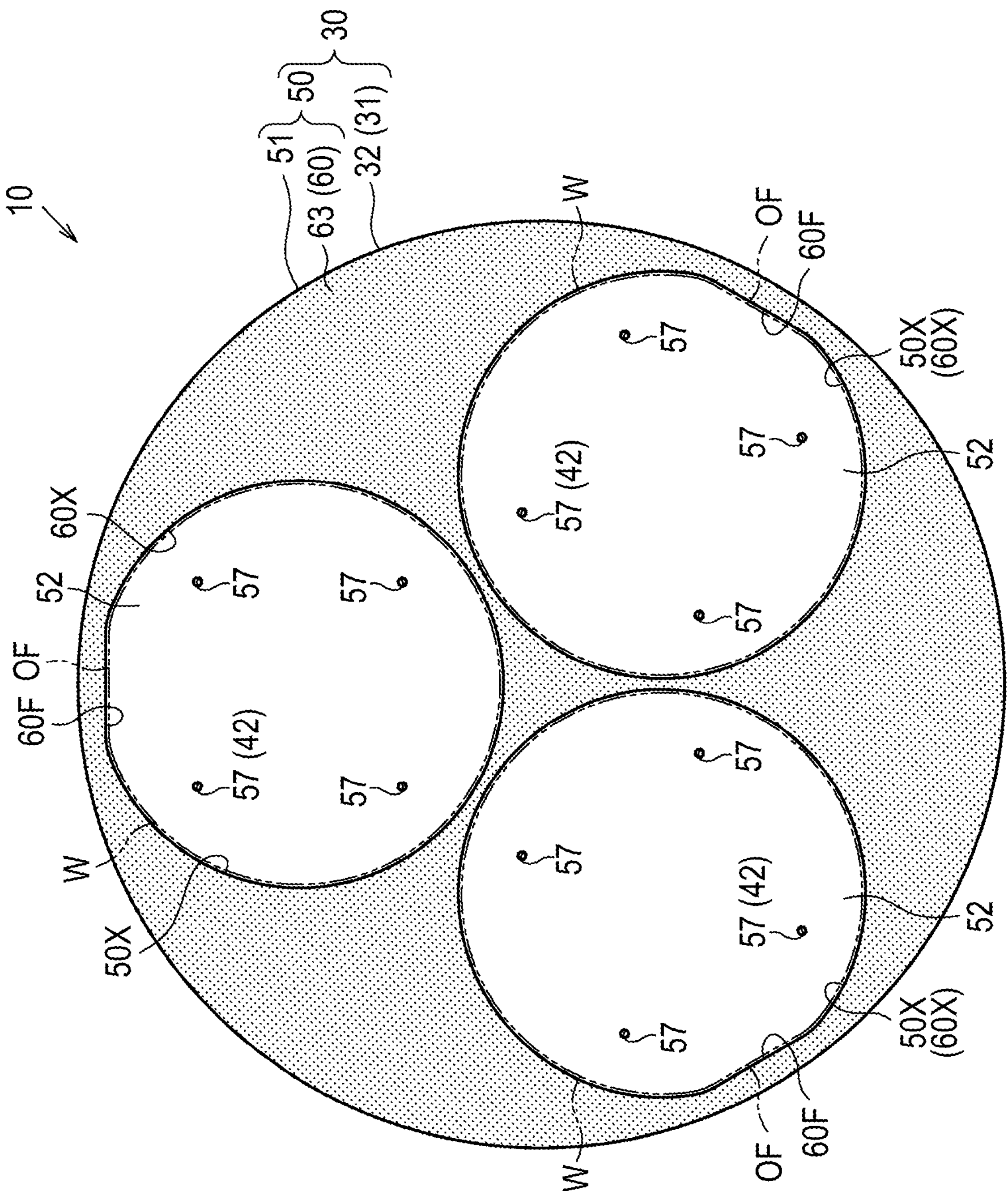


FIG. 1
1
2
3
4
5
G1
G1
10
50X
W
52
60X
W
52
50X
60
51
50
31
30
20

FIG. 2



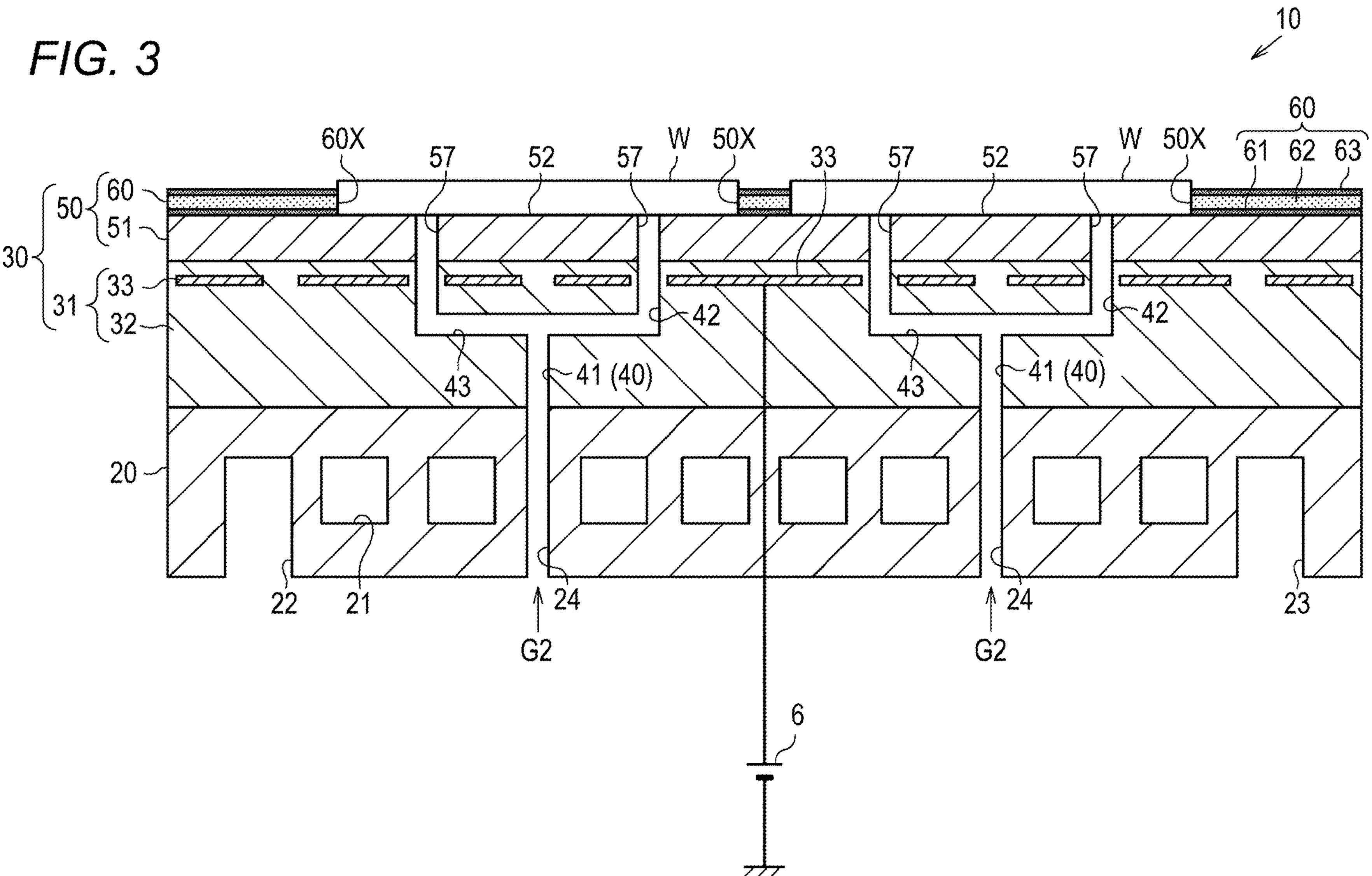


FIG. 3
10
60X
57
52
57
W
50X
33
57
52
57
W
50X
60
61
62
63
50
60
51
30
31
33
32
42
41 (40)
43
42
41 (40)
43
20
22
21
24
G2
24
G2
23
6

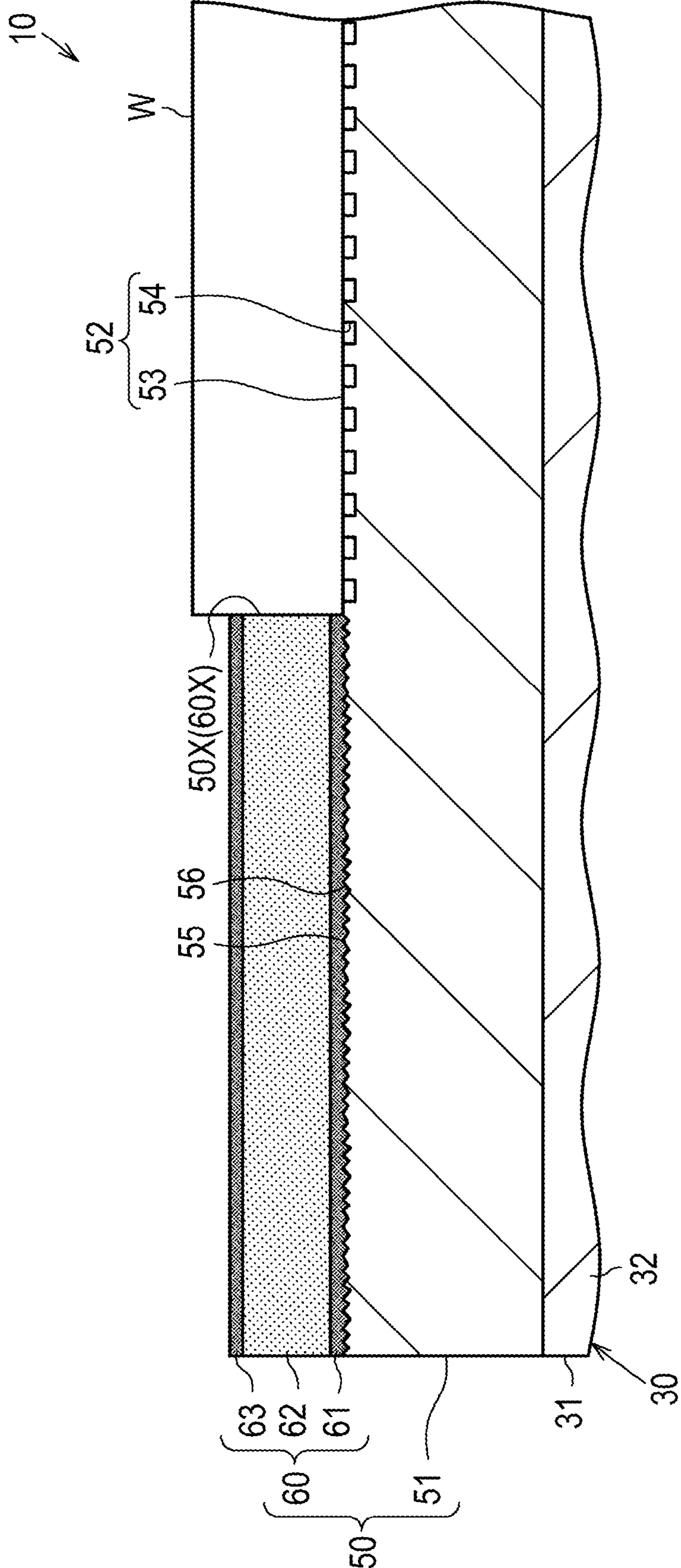


FIG. 4

FIG. 5

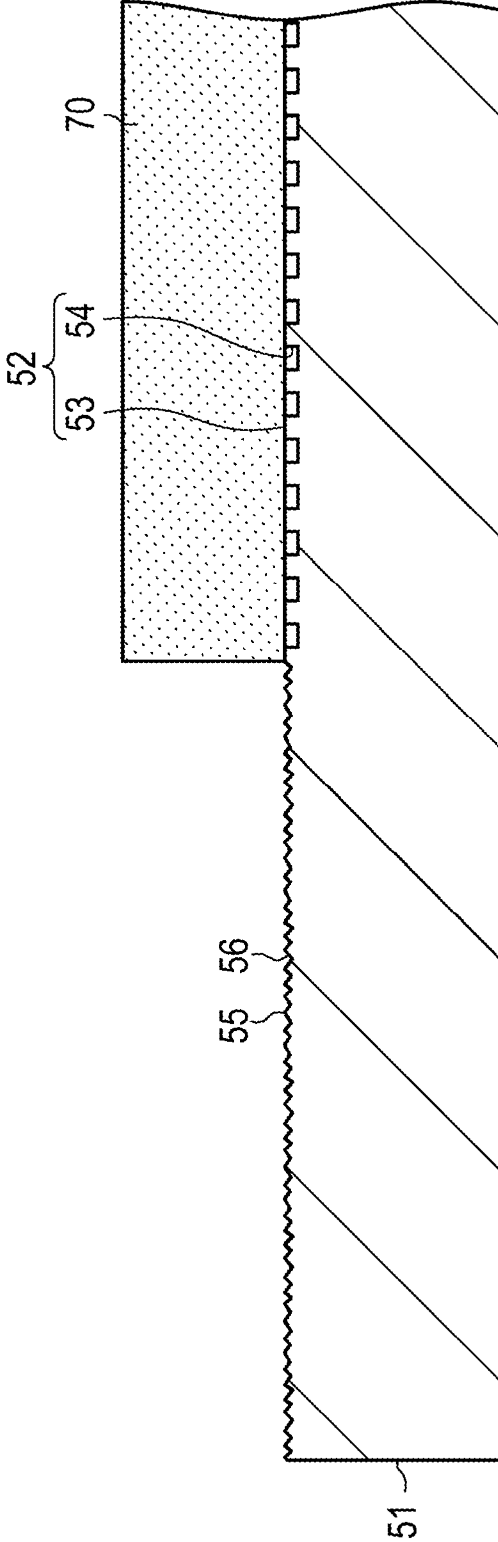


FIG. 6

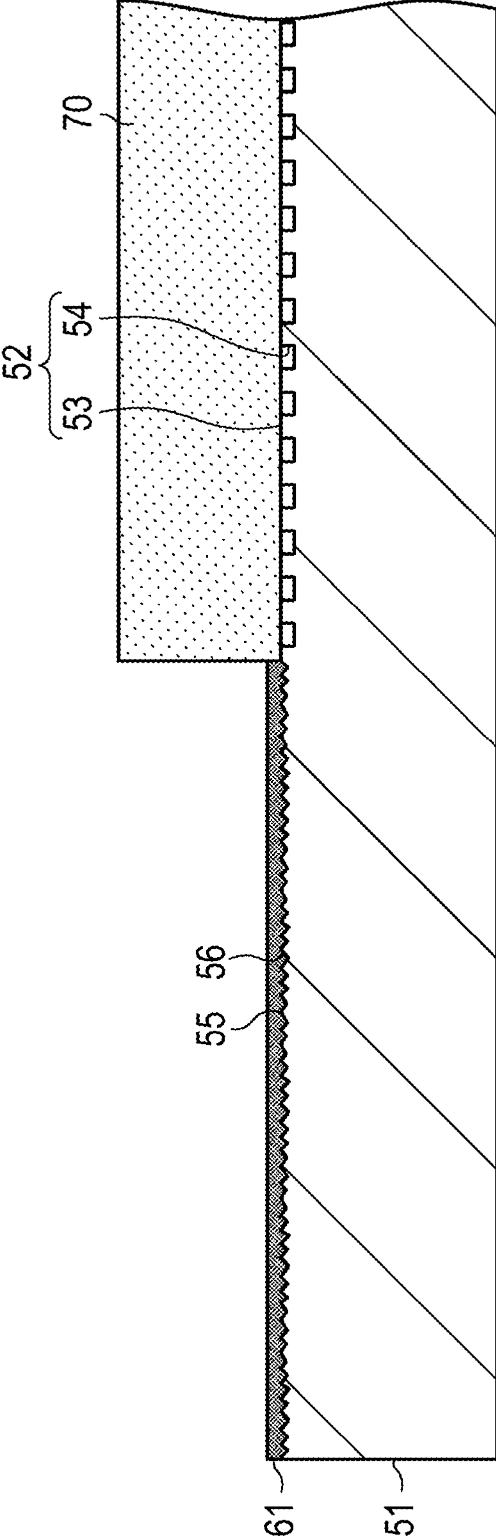


FIG. 7

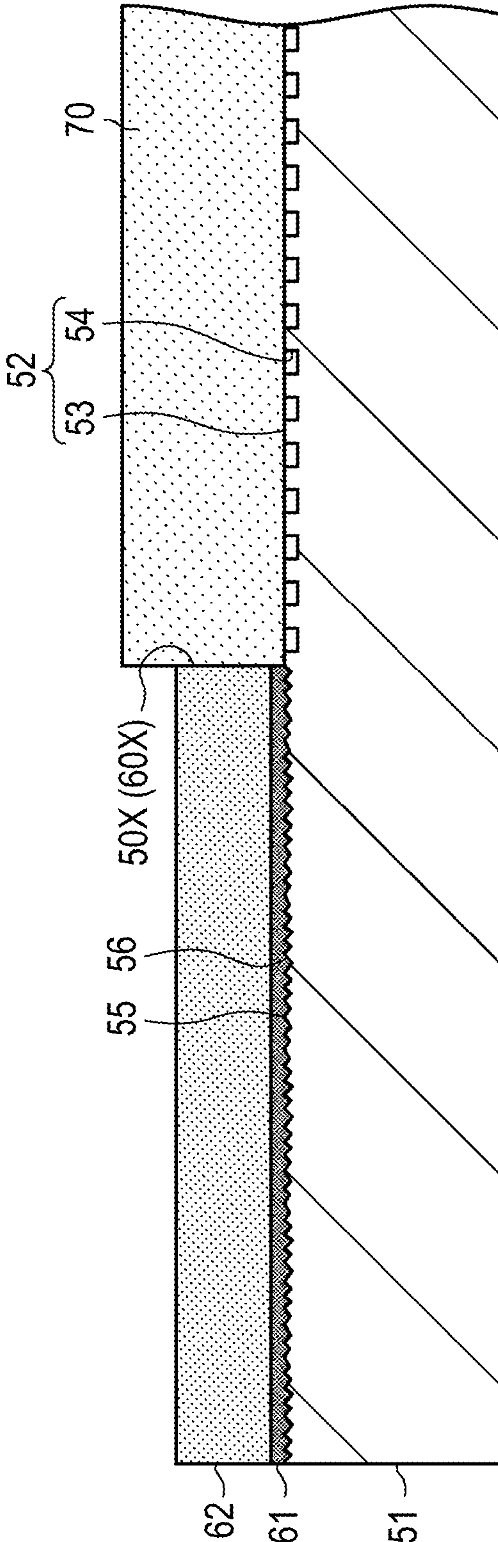


FIG. 8

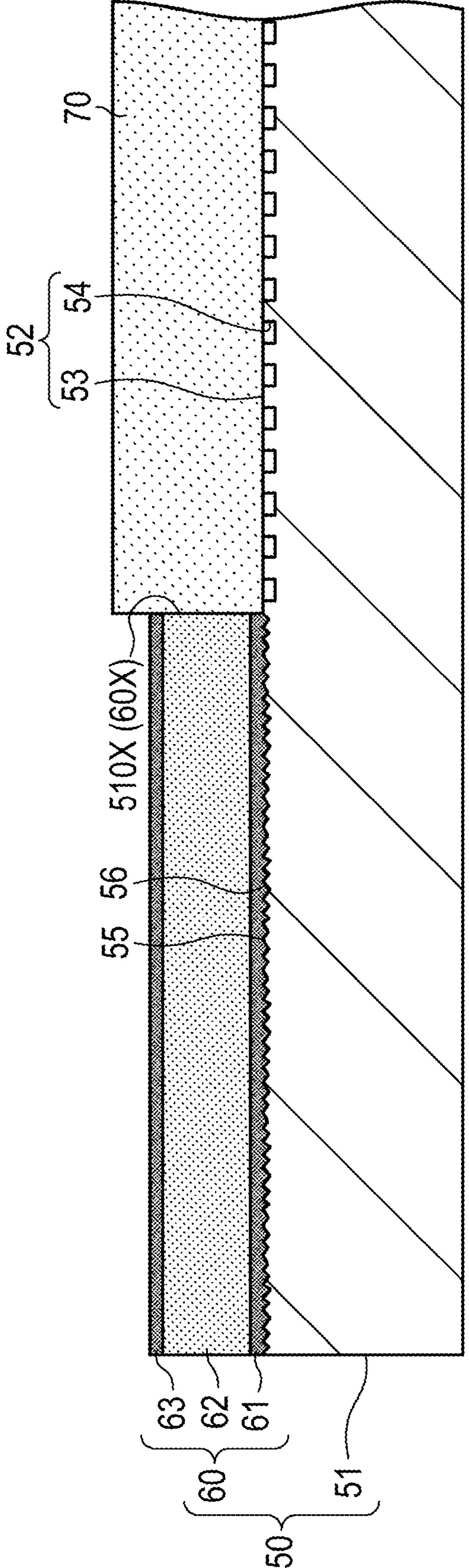
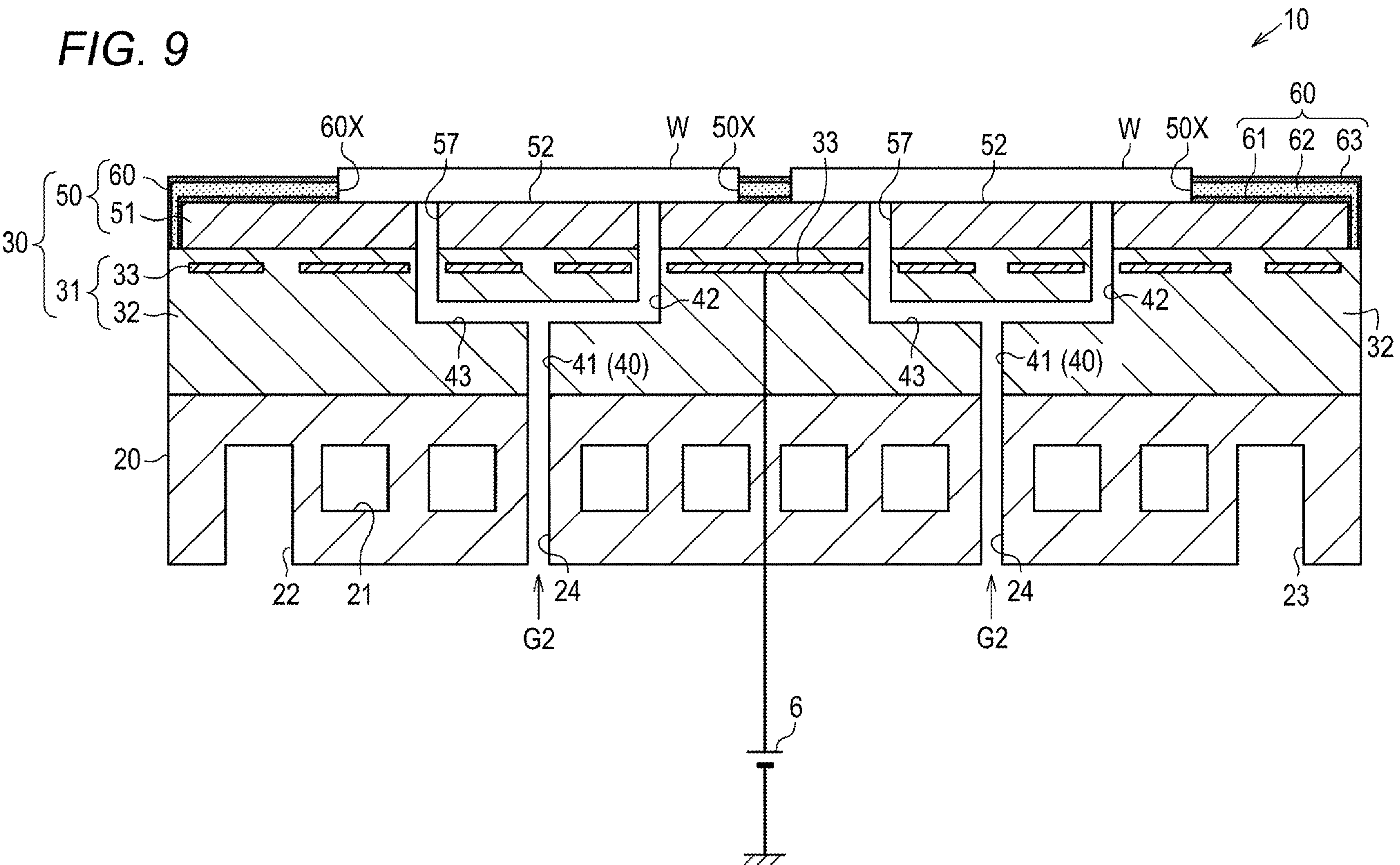


FIG. 9



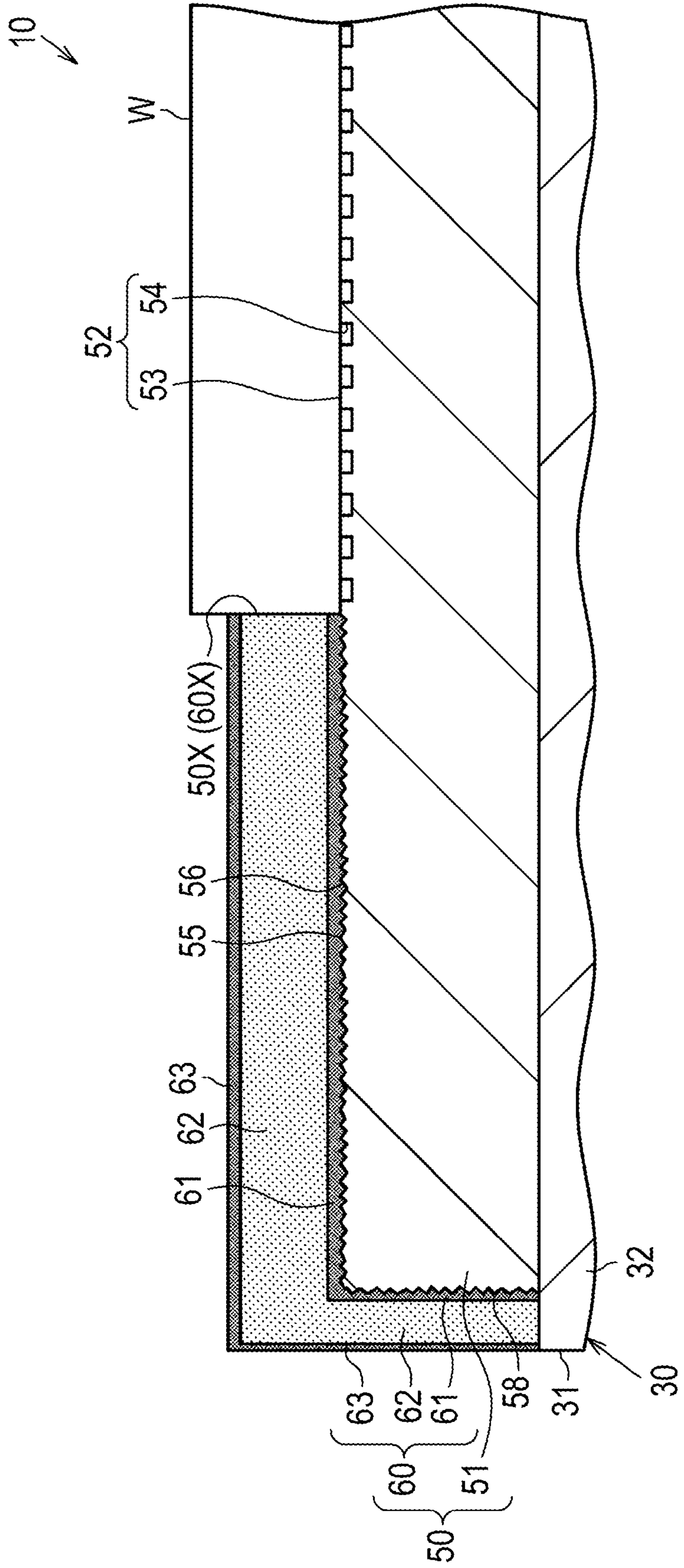


FIG. 10

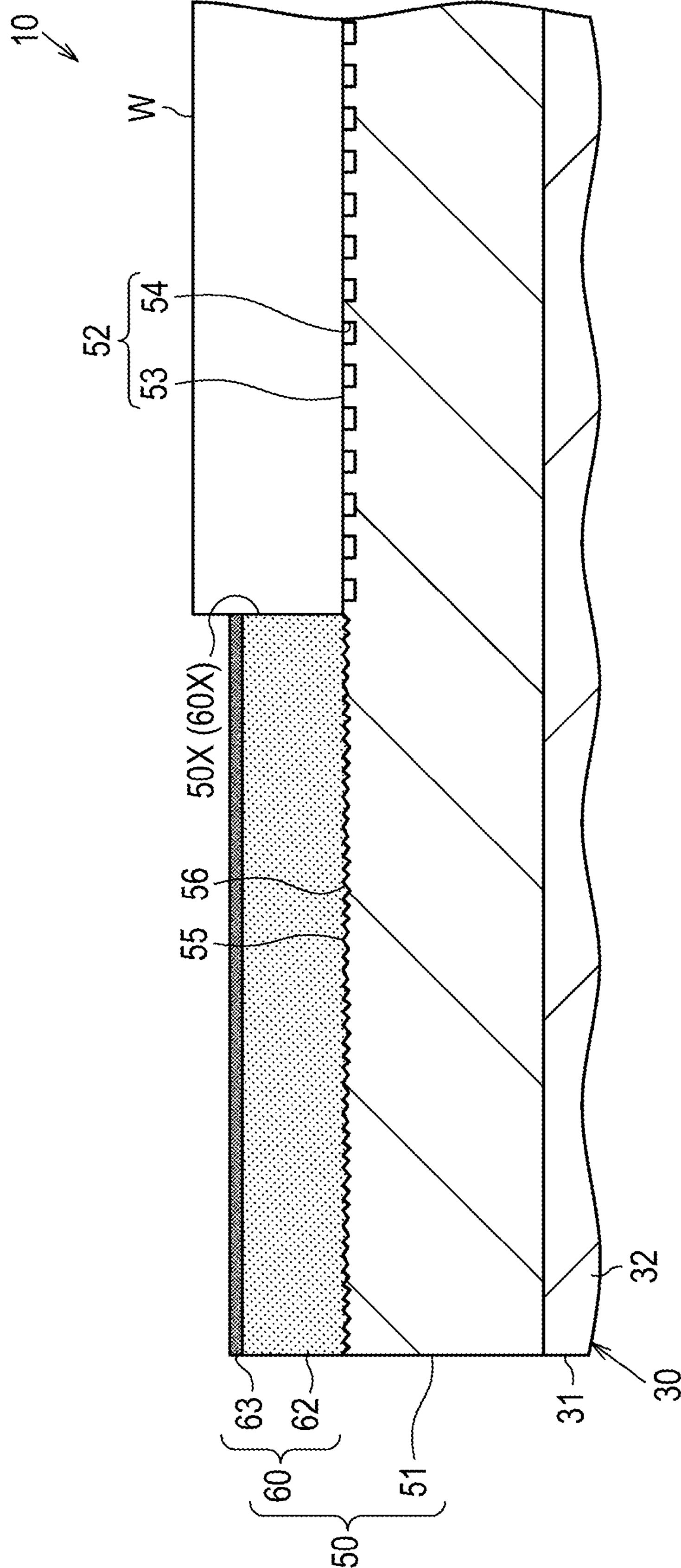
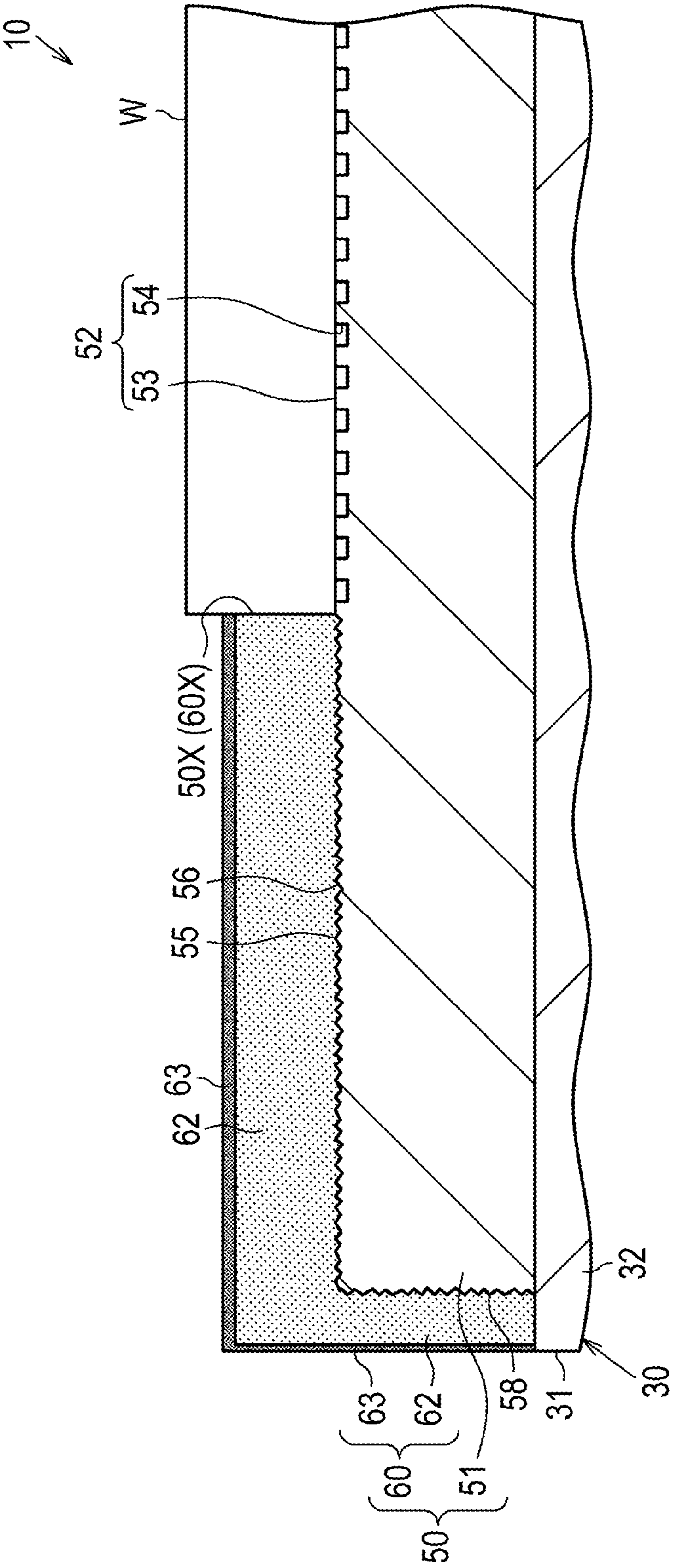


FIG. 11

FIG. 12



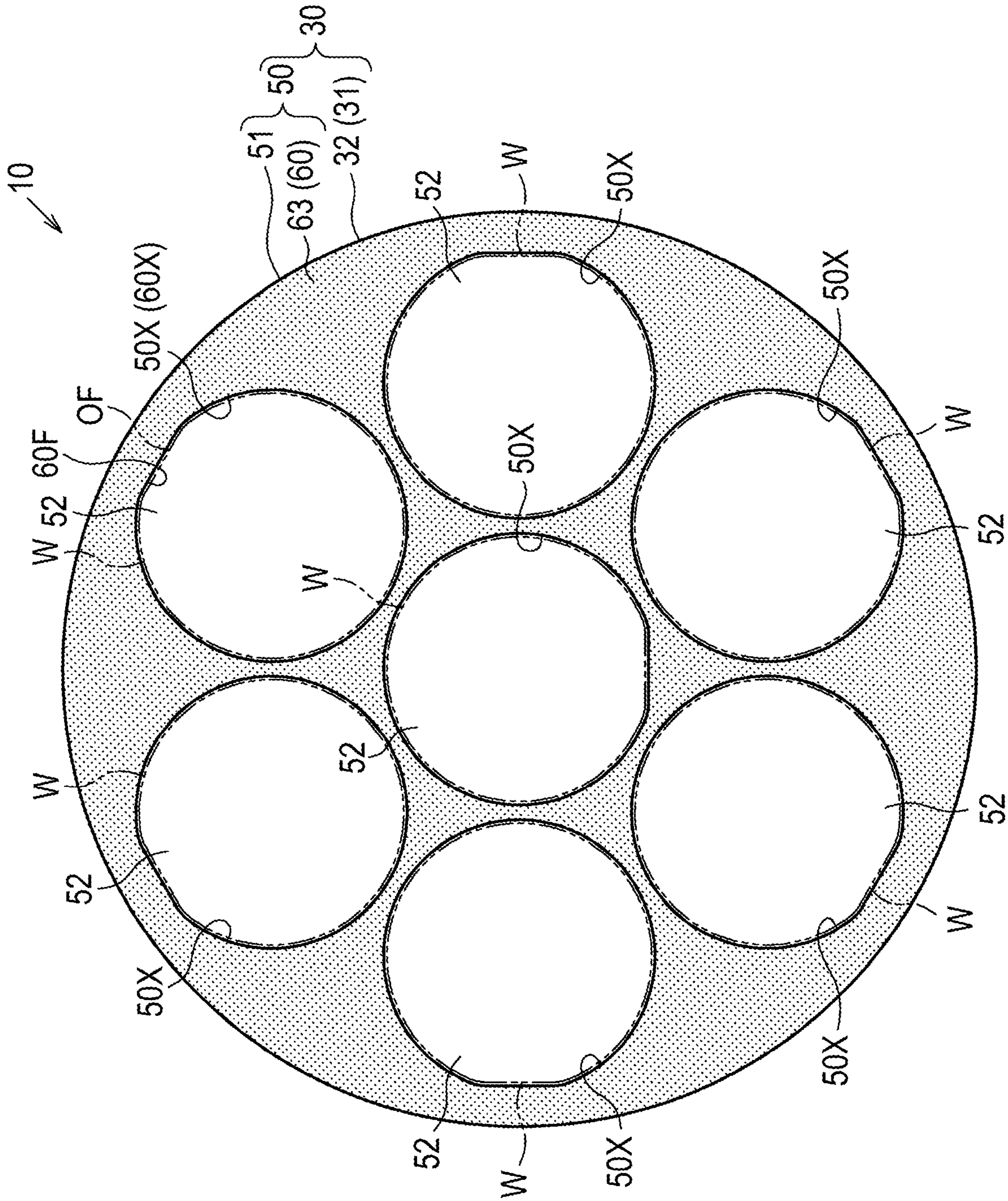


FIG. 13

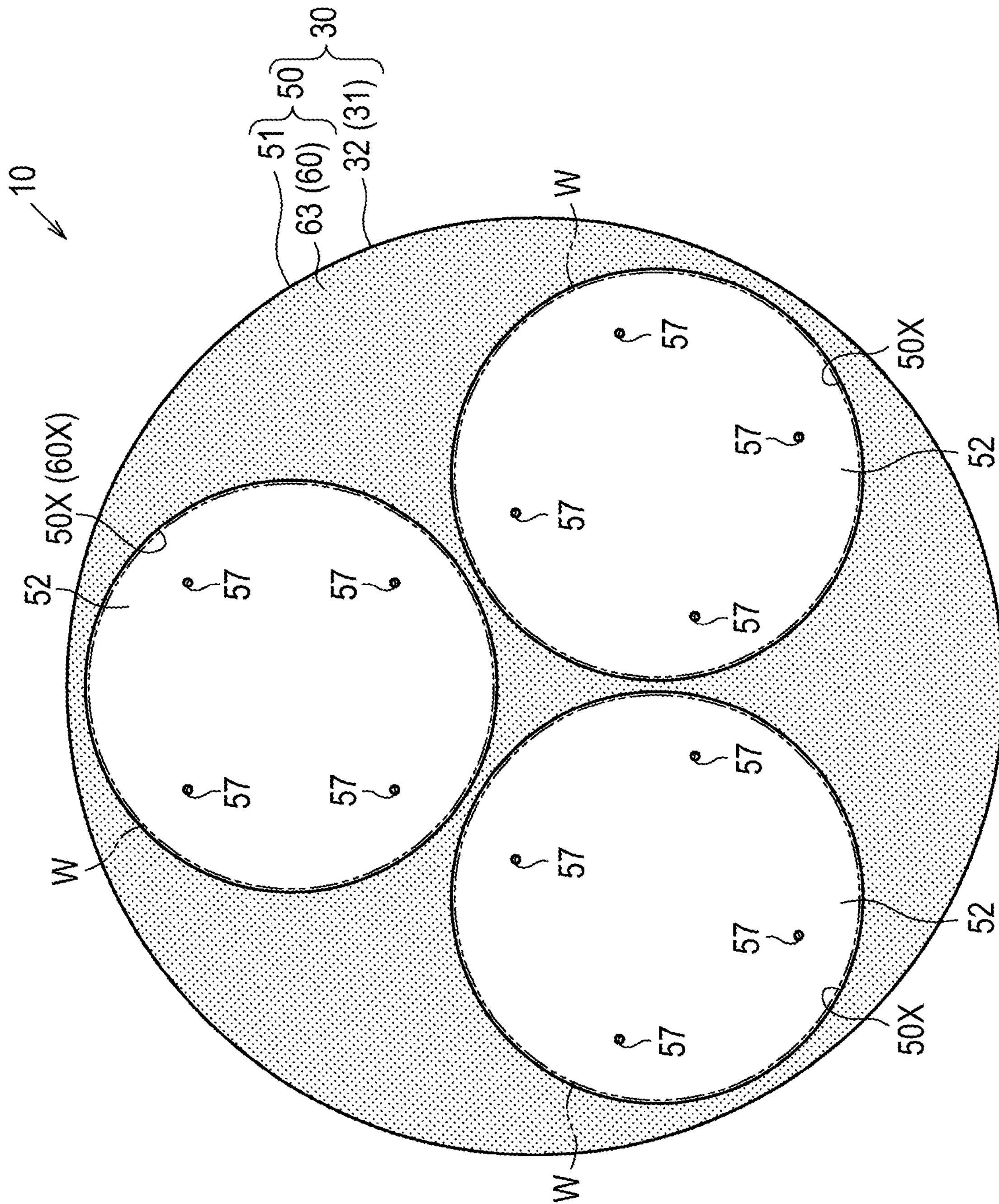


FIG. 14

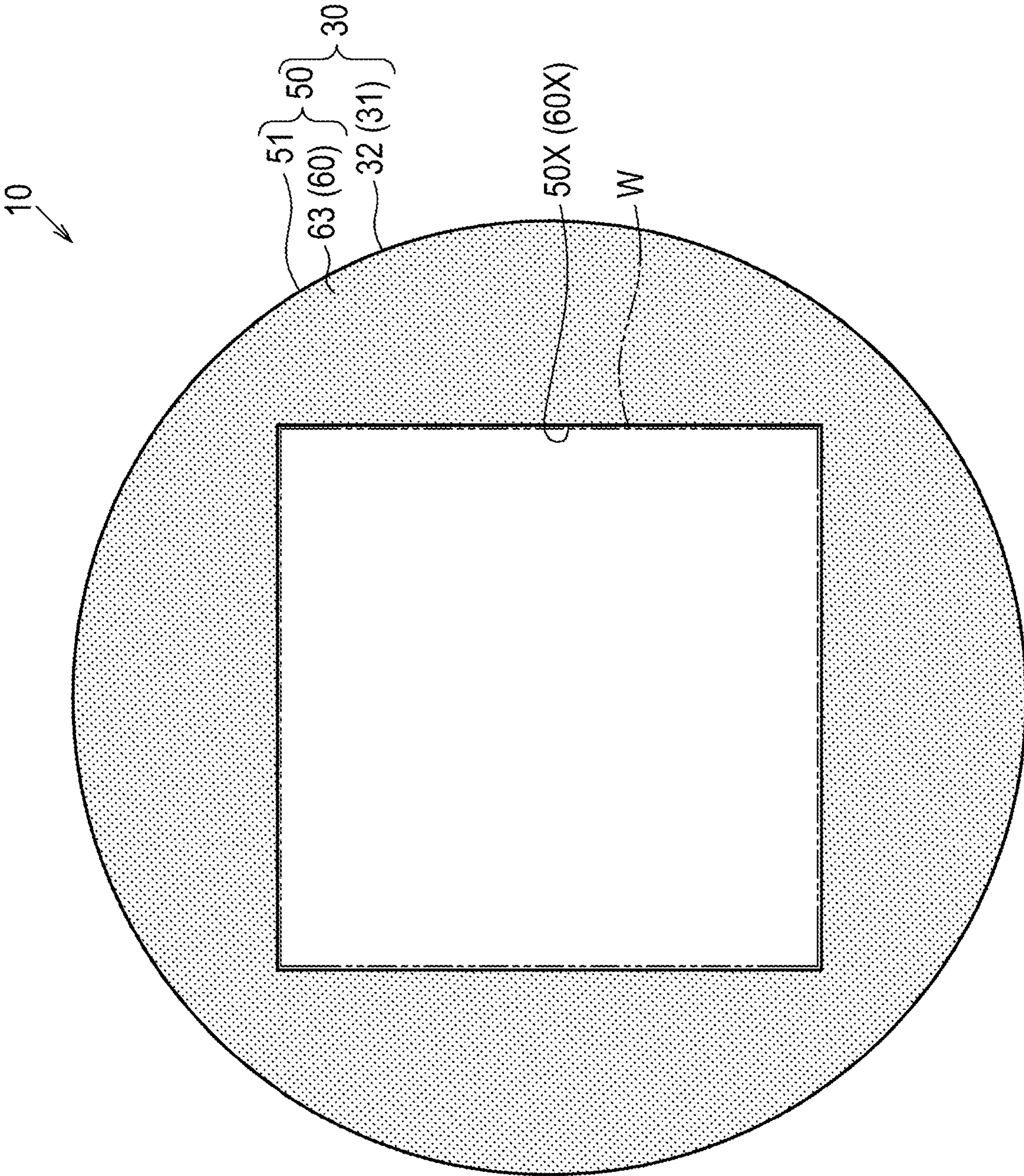
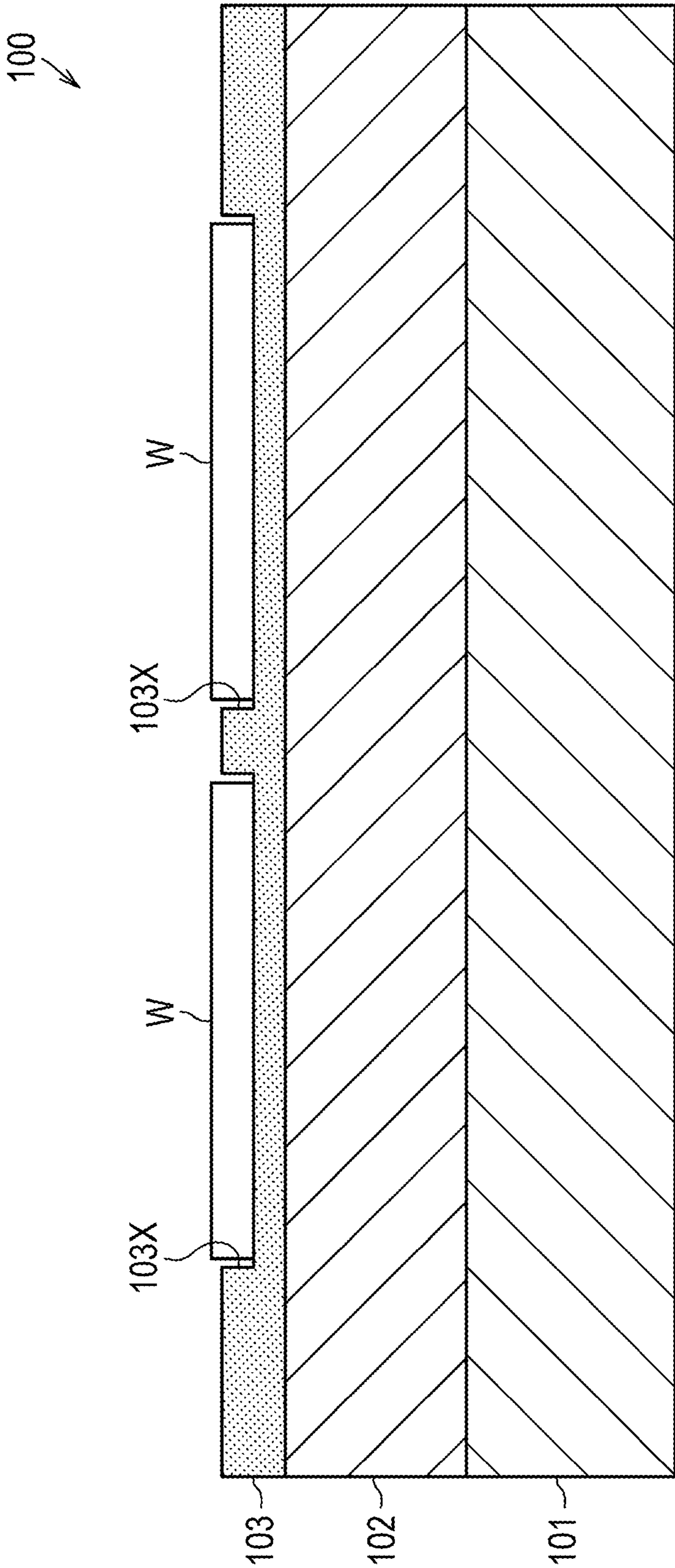


FIG. 15

FIG. 16



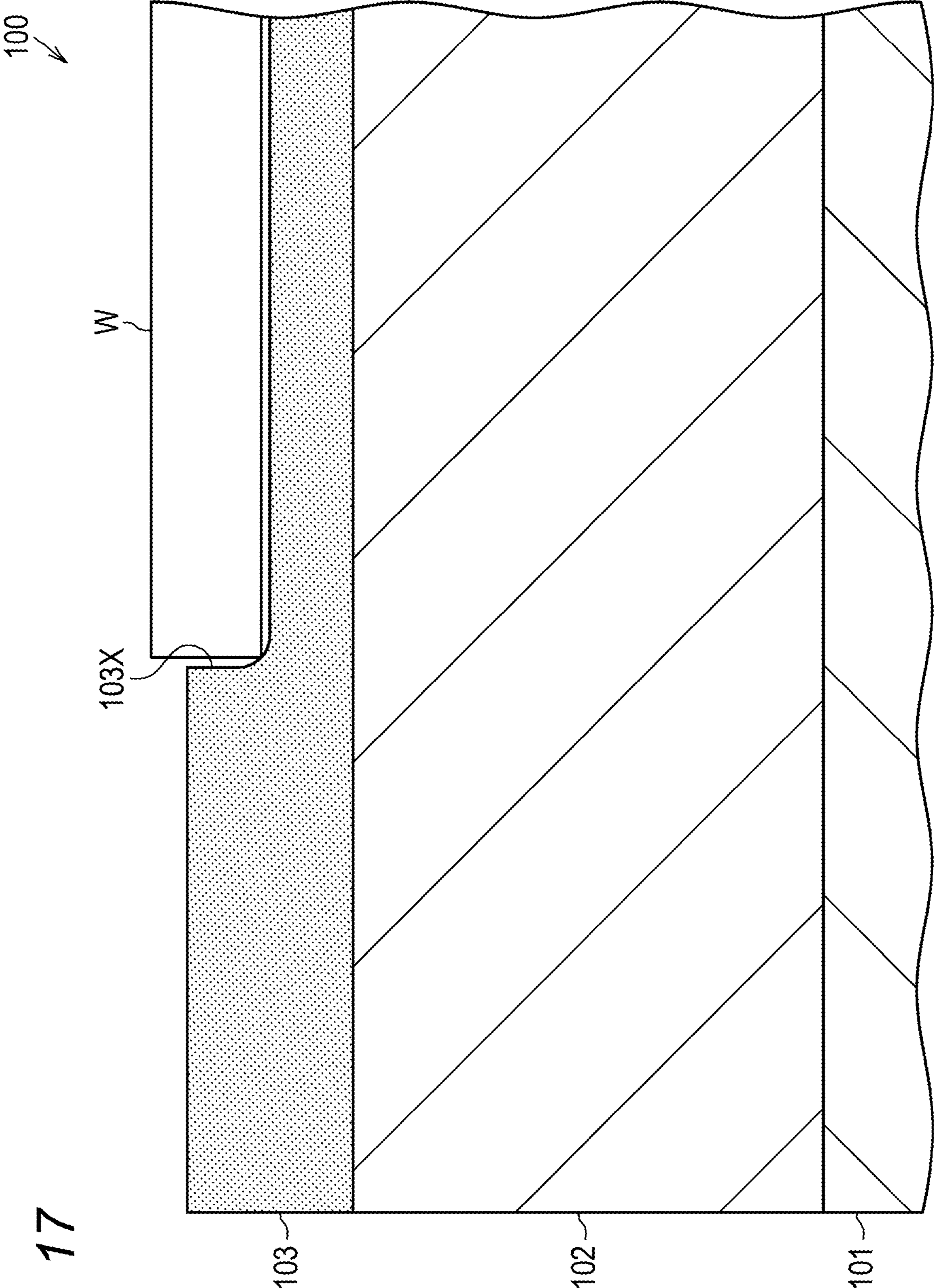


FIG. 17
100
W
103X
103
102
101

TRAY AND SUBSTRATE FIXING DEVICE

CROSS-REFERENCE TO RELATED APPLICATIONS

[0001] This application claims priority from Japanese Patent Application No. 2022-181706, filed on Nov. 14, 2022, the entire content of which is incorporated herein by reference.

TECHNICAL FIELD

[0002] The present invention relates to a tray and a substrate fixing device.

BACKGROUND ART

[0003] In the related art, a semiconductor device such as a light emitting diode (LED) is manufactured by performing various processes such as dry etching and chemical vapor deposition (CVD) on an insulating substrate or a semiconductor substrate. In this process, a plurality of substrates are simultaneously processed using a substrate fixing device for fixing the substrates in a chamber (see, for example, JP2018-142589A). As this type of substrate fixing device, a substrate fixing device using an electrostatic chuck has been proposed.

[0004] As illustrated in FIG. **16**, a substrate fixing device **100** includes a conductive base plate **101**, an electrostatic chuck **102** fixed on the base plate **101**, and a tray **103** sucked to the electrostatic chuck **102**. An upper surface of the tray **103** is provided with a plurality of recesses **103**X for accommodating a plurality of substrates W, respectively.

SUMMARY OF INVENTION

[0005] The recess **103**X of the tray **103** is formed by blasting or the like. As illustrated in FIG. **17**, in the recess **103**X formed by the blasting, an outer peripheral edge of the bottom portion thereof is formed in an R shape. Therefore, in order to accommodate the substrate W in the recess **103**X, it is necessary to increase an opening diameter of the recess **103**X by an amount corresponding to the R shape. However, when the opening diameter of the recess **103**X becomes large, a problem that the substrate W moves in the recess **103**X at the time of transfer or the like occurs. Further, when the substrate W moves in the recess **103**X and the substrate W is placed on an R-shaped portion, the substrate W is inclined in the recess **103**X, and thus there is a problem that the substrate W cannot be sucked.

[0006] According to one aspect of the present invention, there is provided a tray mounted on an electrostatic chuck, and the tray includes: an accommodation recess configured to accommodate a substrate; a bottom plate portion placed on the electrostatic chuck; a coating film layer made of a material different from the bottom plate portion and formed on an upper surface of the bottom plate portion; and an opening portion penetrating the coating film layer in a thickness direction. The accommodation recess includes an inner side surface of the opening portion and an upper surface of the bottom plate portion exposed from the opening portion, the coating film layer has a multilayer structure including a first coating film having higher plasma resistance than the bottom plate portion and a second coating film laminated on an upper surface of the first coating film and having higher plasma resistance than the first coating film, and the first coating film is thicker than the second coating film.

[0007] According to one aspect of the present invention, there is an effect that the substrate can be suitably fixed.

BRIEF DESCRIPTION OF DRAWINGS

[0008] FIG. **1** is a schematic configuration diagram illustrating a semiconductor manufacturing device according to an embodiment.

[0009] FIG. **2** is a schematic plan view illustrating the substrate fixing device according to the embodiment.

[0010] FIG. **3** is a schematic cross-sectional view illustrating a substrate fixing device according to the embodiment.

[0011] FIG. **4** is an enlarged schematic cross-sectional view illustrating a part of the substrate fixing device according to the embodiment.

[0012] FIG. **5** is a schematic cross-sectional view illustrating a method for manufacturing a tray according to the embodiment.

[0013] FIG. **6** is a schematic cross-sectional view illustrating the method for manufacturing a tray according to the embodiment.

[0014] FIG. **7** is a schematic cross-sectional view illustrating the method for manufacturing a tray according to the embodiment.

[0015] FIG. **8** is a schematic cross-sectional view illustrating the method for manufacturing a tray according to the embodiment.

[0016] FIG. **9** is a schematic cross-sectional view illustrating a substrate fixing device according to a modification.

[0017] FIG. **10** is an enlarged schematic cross-sectional view illustrating a part of the substrate fixing device according to the modification.

[0018] FIG. **11** is an enlarged cross-schematic sectional view illustrating a part of the substrate fixing device according to the modification.

[0019] FIG. **12** is an enlarged cross-schematic sectional view illustrating a part of the substrate fixing device according to the modification.

[0020] FIG. **13** is a schematic plan view illustrating the substrate fixing device according to the modification.

[0021] FIG. **14** is a schematic plan view illustrating the substrate fixing device according to the modification.

[0022] FIG. **15** is a schematic plan view illustrating the substrate fixing device according to the modification.

[0023] FIG. **16** is a schematic cross-sectional view illustrating a substrate fixing device of the related art.

[0024] FIG. **17** is an enlarged schematic cross-sectional view illustrating a part of the substrate fixing device of the related art.

DESCRIPTION OF EMBODIMENTS

[0025] Hereinafter, an embodiment will be described with reference to the accompanying drawings.

[0026] In the accompanying drawings, for the sake of convenience, a characteristic portion may be enlarged to facilitate understanding of the characteristic, and a dimensional ratio of each constituent element may be different among the drawings. In addition, in the cross-sectional view, in order to facilitate understanding of the cross-sectional structure of each member, hatching of some members is

illustrated in place of a satin pattern, and hatching of some members is omitted. In this specification, a "plan view" refers to viewing an object from a vertical direction (an upper-lower direction in the drawing) in FIG. **1** and the like, and a "planar shape" refers to a shape of the object viewed from the vertical direction in FIG. **1** and the like. The "upper-lower direction" and a "left-right direction" in the present specification are directions when a direction in which a reference numeral indicating each member in each drawing can be correctly read is defined as a normal position.

[0027] Overall Configuration of Semiconductor Manufacturing Device **1**

[0028] As illustrated in FIG. **1**, a semiconductor manufacturing device **1** includes a chamber **2** and a substrate fixing device **10** accommodated in the chamber **2**. The substrate fixing device **10** fixes substrates W. The semiconductor manufacturing device **1** is, for example, a plasma etching device.

[0029] An upper electrode **3** facing the substrate fixing device **10** is provided at an upper portion of the chamber **2**. The upper electrode **3** also functions as, for example, a shower head for supplying an etching gas G**1** into the chamber **2**. Here, "facing" in the present specification means that surfaces or members are positioned in front of each other, and includes not only a case where surfaces or members are completely positioned in front of each other but also a case where surfaces or members are partially positioned in front of each other. In addition, "facing" in this specification includes both a case where a member different from the two portions is interposed between the two portions and a case where nothing is interposed between the two portions.

[0030] A discharge port **4** is provided in a lower portion of the chamber **2**. The etching gas G**1** is discharged from the discharge port **4** to the outside of the chamber **2**.

[0031] Configuration of Substrate W

[0032] As illustrated in FIG. **2**, a plurality of (here, three) substrates W are fixed to the substrate fixing device **10**. Each substrate W is an object to be fixed to the substrate fixing device **10**. Each substrate W is, for example, a silicon wafer. A planar shape of each substrate W can be any shape and any size. The planar shape of each substrate W is, for example, a circular shape as a whole. Each substrate W has, for example, an orientation flat OF. A diameter of the substrate W may be, for example, about 100 mm to 150 mm.

[0033] Overall Configuration of Substrate Fixing Device **10**

[0034] As illustrated in FIG. **1**, the substrate fixing device **10** includes a conductive base plate **20** and a substrate fixture **30** mounted on the base plate **20**. The base plate **20** is a base member for mounting the substrate fixture **30**.

[0035] The substrate fixture **30** includes an electrostatic chuck **31** and a tray **50** mounted on an upper surface of the electrostatic chuck **31**. The tray **50** has, for example, a plurality of accommodation recesses **50**X that respectively accommodate a plurality of substrates W. The electrostatic chuck **31** sucks and holds the tray **50** that accommodates the plurality of substrates W. In addition, the electrostatic chuck **31** is, for example, a temperature adjusting device that adjusts a temperature of the substrate W accommodated in the tray **50**.

[0036] Configuration of Base Plate **20**

[0037] The base plate **20** is formed in a circular plate shape, for example. A planar shape of the base plate **20** may be, for example, circular. A diameter of the base plate **20** may be, for example, about 200 mm to 450 mm. A thickness of the base plate **20** may be, for example, about 20 mm to 50 mm. As a material of the base plate **20**, for example, a metal material such as aluminum or a super hard alloy, a composite material of the metal material and a ceramic material, or the like can be used.

[0038] The base plate **20** is connected to, for example, a high-frequency power supply **5**. The base plate **20** functions as, for example, a lower electrode for controlling plasma. For example, a predetermined high-frequency power is supplied from the high-frequency power supply **5** to the base plate **20**.

[0039] In the semiconductor manufacturing device **1**, the etching gas G**1** is turned into plasma by applying the high-frequency power to the base plate **20** in a state in which the inside of the chamber **2** is depressurized while maintaining the upper electrode **3** at a ground potential, and accordingly the substrate W is plasma-etched.

[0040] As illustrated in FIG. **3**, for example, a cooling path **21** is provided inside the base plate **20**. The cooling path **21** includes an introduction portion **22** provided at one end thereof and a discharge portion **23** provided at the other end thereof. The cooling path **21** is connected to, for example, a cooling medium control device (not illustrated) provided outside the substrate fixing device **10**. The cooling medium control device introduces a cooling medium from the introduction portion **22** into the cooling path **21** and discharges the cooling medium from the discharge portion **23**. By circulating the cooling medium through the cooling path **21** to cool the base plate **20**, the tray **50** and the substrate W sucked on the electrostatic chuck **31** can be cooled. As the cooling medium, for example, water or Galden can be used.

[0041] For example, gas paths **24** for introducing an inert gas G**2** for cooling are provided inside the base plate **20**. The base plate **20** has a plurality of gas paths **24** respectively corresponding to the plurality of accommodation recesses **50**X of the tray **50**. The base plate according to the present embodiment has three gas paths **24**. The inert gas G**2** is a gas for cooling each substrate W accommodated in the accommodation recess **50**X of the tray **50**. As the inert gas G**2**, for example, helium gas can be used.

[0042] Configuration of Electrostatic Chuck **31**

[0043] The electrostatic chuck **31** has, for example, a circular plate shape. A planar shape of the electrostatic chuck **31** may be, for example, a circular. A diameter of the electrostatic chuck **31** may be, for example, equal to or smaller than the diameter of the base plate **20**. The diameter of the electrostatic chuck **31** according to the present embodiment is equal to the diameter of the base plate **20**. The diameter of the electrostatic chuck **31** may be, for example, about 200 mm to 450 mm. A thickness of the electrostatic chuck **31** may be, for example, about 3 mm to 5 mm. In the present specification, "equal" includes not only a case of being accurately equal but also a case where there is a slight difference between comparison targets due to an influence in a dimensional tolerance or the like.

[0044] The electrostatic chuck **31** includes a base body **32** and an electrostatic electrode **33** built in the base body **32**. The electrostatic chuck **31** sucks the tray **50** and the substrate W by an electrostatic force. The electrostatic chuck **31** is, for

example, a Johnsen-Rahbeck type electrostatic chuck. The electrostatic chuck **31** may be a Coulomb force type electrostatic chuck.

[0045] The base body **32** is bonded to an upper surface of the base plate **20** by an adhesive (not illustrated). Accordingly, the electrostatic chuck **31** is fixed to the upper surface of the base plate **20**. As the adhesive, for example, a silicone-based adhesive can be used.

[0046] As a material of the base body **32**, for example, a material having an insulating property can be used. For example, ceramics such as alumina, aluminum nitride, and silicon nitride, and organic materials such as silicone resin and polyimide resin can be used as the material of the base body **32**. In the present embodiment, ceramics such as alumina or aluminum nitride is adopted as the material of the base body **32** in terms of availability, ease of processing, and relatively high resistance to plasma or the like.

[0047] The electrostatic electrode **33** is an electrode formed in a thin film shape. The electrostatic electrode **33** is an electrode for sucking the tray **50** and the substrate W. The electrostatic electrode **33** is built in the base body **32**. The electrostatic electrode **33** is built in, for example, a portion positioned in the vicinity of the upper surface of the base body **32** in a thickness direction of the base body **32**. The electrostatic electrode **33** is disposed, for example, on a plane parallel to the upper surface of the base body **32**. The electrostatic electrode **33** is electrically connected to a power supply **6** for sucking provided outside the substrate fixing device **10**. When a predetermined voltage is applied from the power supply **6** for sucking, the electrostatic electrode **33** generates a suction force by electrostatic electricity between the tray **50** mounted on the upper surface of the base body **32** and the electrostatic electrode **33**. Accordingly, the tray **50** accommodating the plurality of substrates W can be sucked and held on the upper surface of the base body **32**. A suction and holding force of the electrostatic chuck **31** increases as the voltage applied to the electrostatic electrode **33** increases. The electrostatic electrode **33** may have a unipolar shape or a bipolar shape. As the material of the electrostatic electrode **33**, for example, tungsten (W) or molybdenum (Mo) can be used.

[0048] For example, gas holes **40** communicating with the gas paths **24** of the base plate **20** are provided inside the base body **32**. The base body **32** has a plurality of gas holes **40** respectively corresponding to the plurality of accommodation recesses **50**X. The base body **32** according to the present embodiment has three gas holes **40**. Each gas hole **40** is formed so as to penetrate the base body **32** in the thickness direction. Each gas hole **40** is provided so as to overlap the accommodation recess **50**X in a plan view. An opening end of each gas hole **40** is provided so as to be exposed on the upper surface of the base body **32**. For example, the inert gas G2 is introduced into each gas hole **40** from the corresponding gas path **24**.

[0049] Each gas hole **40** includes, for example, a first hole portion **41** extending from a lower surface toward the upper surface of the base body **32**, second hole portions **42** extending from the upper surface toward the lower surface of the base body **32**, and a third hole portion **43** communicating the first hole portion **41** with the second hole portions **42**.

[0050] The first hole portion **41** is formed so as to open downward of the base body **32**. The first hole portion **41** is formed to linearly extend along the thickness direction of the base body **32**, for example. A lower end portion of the first hole portion **41** communicates with the gas path **24**. An upper end portion of the first hole portion **41** communicates with the third hole portion **43**. A shape and a size of the first hole portion **41** can be any shape and any size.

[0051] The second hole portion **42** is formed so as to open above the base body **32**. The second hole portion **42** is formed to linearly extend along the thickness direction of the base body **32**, for example. A lower end portion of the second hole portion **42** communicates with the third hole portion **43**. A shape and a size of the second hole portion **42** can be any shape and any size.

[0052] The plurality of second hole portions **42** are provided apart from each other in a plan view. In this example, for example, four second hole portions **42** are provided for each of the three accommodation recesses **50**X.

[0053] The third hole portion **43** is provided between the first hole portion **41** and the second hole portion **42** in the thickness direction of the base body **32**. The third hole portion **43** is formed so as to extend in a planar direction (left-right direction in the drawing) of the base body **32**. The third hole portion **43** is formed, for example, so as to communicate one first hole portion **41** with a plurality of (here, four) second hole portions **42**. A shape and a size of the third hole portion **43** can be any shape and any size.

[0054] Configuration of Tray **50**

[0055] The tray **50** is mounted on the upper surface of the base body **32**. The tray **50** is formed to cover the upper surface of the base body **32**.

[0056] The tray **50** has a bottom plate portion **51**, a coating film layer **60** formed on an upper surface of the bottom plate portion **51**, and opening portions **60**X penetrating the coating film layer **60** in the thickness direction. The coating film layer **60** is made of a material different from that of the bottom plate portion **51**.

[0057] The bottom plate portion **51** is formed in a plate shape, for example. The bottom plate portion **51** is formed in a circular plate shape, for example. A planar shape of the bottom plate portion **51** may be, for example, circular. A diameter of the bottom plate portion **51** may be equal to or smaller than the diameter of the electrostatic chuck **31**, for example. The diameter of the bottom plate portion **51** according to the present embodiment is equal to the diameter of the electrostatic chuck **31**. The diameter of the bottom plate portion **51** may be, for example, about 200 mm to 450 mm. A thickness of the bottom plate portion **51** may be, for example, about 3 mm to 5 mm.

[0058] As a material of the bottom plate portion **51**, for example, an insulating material can be used. For example, ceramics such as alumina, aluminum nitride, and silicon nitride can be used as the material of the bottom plate portion **51**. The bottom plate portion **51** of this example is a ceramic substrate. The bottom plate portion **51** has, for example, a lower volume resistivity than the base body **32**. For example, the bottom plate portion **51** is formed of only alumina to which titanium is added as an impurity, and the volume resistivity of the bottom plate portion **51** is set to be equal to or lower than the volume resistivity of the base body **32** by increasing a concentration of titanium.

[0059] The bottom plate portion **51** has an upper surface and a lower surface opposite to the upper surface in a thickness direction of the bottom plate portion **51**. A lower surface of the bottom plate portion **51** is in contact with the upper surface of the base body **32**. The upper surface of the

bottom plate portion **51** has a plurality of substrate placement portions **52** on which each of the plurality of substrates W is placed. The upper surface of the bottom plate portion **51** according to the present embodiment has three substrate placement portions **52**. The substrate placement portion **52** is provided in a portion of the upper surface of the bottom plate portion **51** exposed from the opening portion **60**X of the coating film layer **60**.

[0060] As illustrated in FIG. **4**, each substrate placement portion **52** is provided with a plurality of embossed portions **53**. The plurality of embossed portions **53** are provided, for example, side by side along a planar direction of the bottom plate portion **51** (that is, a direction orthogonal to the thickness direction of the bottom plate portion **51** in a cross-sectional view). The plurality of embossed portions **53** are formed by, for example, providing a plurality of recesses **54** recessed from the upper surface of the bottom plate portion **51** toward the electrostatic chuck **31**. Each of the recesses **54** is formed, for example, so as to extend from the upper surface of the bottom plate portion **51** to the middle of the bottom plate portion **51** in the thickness direction. The plurality of embossed portions **53** and the plurality of recesses **54** are provided, for example, so as to spread over the entire substrate placement portion **52**.

[0061] The upper surface of the bottom plate portion **51** has, for example, a roughened surface **55**. The roughened surface **55** is provided on a portion of the upper surface of the bottom plate portion **51** that overlaps the coating film layer **60** in a plan view. In other words, the roughened surface **55** is provided on a portion of the upper surface of the bottom plate portion **51** other than the substrate placement portions **52**. The roughened surface **55** is provided, for example, so as to partition areas of the three substrate placement portions **52**. The roughened surface **55** is formed so as to surround each of the three substrate placement portions **52** in a plan view, for example. The roughened surface **55** is formed to have a surface roughness larger than that of the lower surface of the bottom plate portion **51**, for example. In the roughened surface **55**, for example, a recess **56** constituting the roughened surface **55** is shallower than the recess **54** of the substrate placement portion **52**. The roughened surface **55** can have a surface roughness Ra of 800 nm or more, for example. Here, the surface roughness Ra value is a kind of numerical value representing the surface roughness and is referred to as an arithmetic average roughness, and specifically is a value obtained by measuring an absolute value of a height changing in a measurement area from a surface which is an average line and performing arithmetic averaging.

[0062] As illustrated in FIG. **3**, for example, a gas hole **57** communicating with the gas hole of the electrostatic chuck **31** is provided inside the bottom plate portion **51**. The bottom plate portion **51** is provided with a plurality of gas holes **57** communicating with the plurality of second hole portions **42** of the gas hole **40**. Each gas hole **57** is formed so as to penetrate through the bottom plate portion **51** in the thickness direction. Each gas hole **57** is formed so as to penetrate from the lower surface to the upper surface of the bottom plate portion **51**. Each gas hole **57** is provided so as to overlap the substrate placement portion **52** in a plan view. That is, each gas hole **57** is provided so as to overlap the substrate W placed on the substrate placement portion **52** in a plan view. An opening end of each gas hole **57** is provided so as to be exposed to the substrate placement portion **52**. For example, the inert gas G**2** is introduced into each gas hole **57** from the corresponding gas hole **40**.

[0063] The gas hole **57** is formed to linearly extend along the thickness direction of the bottom plate portion **51**, for example. The gas hole **57** is formed, for example, so as to open below the bottom plate portion **51** and open above the bottom plate portion **51**. A lower end portion of the gas hole **57** communicates with the second hole portion **42** of the gas hole **40**. The upper end portion of the gas hole **57** is a discharge port of the gas hole **57** for discharging the inert gas G**2** to the outside of the gas hole **57**. A shape and a size of the gas hole **57** can be any shape and any size.

[0064] As illustrated in FIG. **2**, the plurality of gas holes **57** are provided apart from each other in a plan view. For example, four gas holes **57** are provided for each of the three substrate placement portions **52**. The four gas holes **57** are dispersedly provided on each substrate placement portion **52**. For example, the four gas holes **57** are dispersedly provided in four directions of each substrate placement portion **52** in a plan view. For example, the four gas holes **57** are provided on the same circumference in a plan view.

[0065] As illustrated in FIG. **3**, in the gas holes **40** and **57**, the inert gas G2 is introduced into the first hole portion **41** of the gas hole **40** through the gas path **24**, and the inert gas G2 flows into the third hole portion **43** through the first hole portion **41**. In addition, in the gas holes **40** and **57**, the inert gas G2 flowing into the third hole portion **43** is moved in the third hole portion **43** in the planar direction and then flows into the second hole portion **42**, and the inert gas G2 flows into the gas hole **57** through the second hole portions **42**. Then, the inert gas G2 is discharged from the upper end portions of the gas holes **57**. The inert gas G2 discharged from the gas holes **57** can cool the substrate W by, for example, being filled between a lower surface of the substrate W placed on the substrate placement portion **52** and the substrate placement portion **52**. Here, the embossed portions **53** and the recesses **54** (see FIG. **4**) provided in the substrate placement portion **52** act to make the flow of the inert gas G2 uniform. Therefore, an amount of the inert gas G2 hitting the lower surface of the substrate W can be made uniform.

[0066] The coating film layer **60** has a function of fixing the plurality of substrates W on the bottom plate portion **51**. In addition, the coating film layer **60** has a function of protecting the bottom plate portion **51** and the base body **32** of the electrostatic chuck **31** from erosion due to plasma irradiation when plasma treatment is performed in the semiconductor manufacturing device **1** (see FIG. **1**) in an environment using a process gas having high erosion resistance.

[0067] As illustrated in FIG. **4**, the coating film layer **60** is formed to cover the roughened surface **55** of the upper surface of the bottom plate portion **51**. The coating film layer **60** is formed in close contact with the roughened surface **55**. As illustrated in FIG. **2**, the coating film layer **60** is formed to cover a portion of the upper surface of the bottom plate portion **51** other than the substrate placement portion **52**. In other words, the coating film layer **60** has the opening portions **60**X that expose the substrate placement portions **52**. The coating film layer **60** according to the present embodiment has three opening portions **60**X that respectively expose the three substrate placement portions **52**. Each opening portion **60**X is formed to define the area of each substrate placement portion **52**. The planar shape of each opening portion **60**X is formed in a shape correspond-

ing to the planar shape of the substrate W. The planar shape of each opening portion **60**X is formed in a circular shape as a whole. The planar shape of each opening portion **60**X has, for example, a flat portion **60**F corresponding to the orientation flat OF of the substrate W. A size of the planar shape of each opening portion **60**X is equal to or slightly larger than the size of the planar shape of the substrate W. The substrate W is accommodated in the opening portion **60**X such that, for example, the orientation flat OF is aligned with the flat portion **60**F of the opening portion **60**X. Accordingly, the substrate W can be accommodated in the opening portion **60**X in a state in which the orientation flat OF of the substrate W faces a desired direction.

[0068] As illustrated in FIG. **3**, in the tray **50**, an inner side surface of the opening portion **60**X of the coating film layer **60** and the upper surface of the bottom plate portion **51** exposed from the opening portion **60**X, that is, the upper surface of the bottom plate portion **51** constituting the substrate placement portion **52** constitute the accommodation recess **50**X for accommodating the substrate W.

[0069] As illustrated in FIG. **4**, the coating film layer **60** is formed in a multilayer structure including a coating film **61** formed on the upper surface of the bottom plate portion **51**, a coating film **62** laminated on an upper surface of the coating film **61**, and a coating film **63** laminated on an upper surface of the coating film **62**. As materials of the coating films **61**, **62**, and **63**, a material having higher durability against plasma, that is, plasma resistance than the material (for example, alumina) constituting the bottom plate portion **51** can be used. As the materials of the coating films **61**, **62**, and **63**, for example, a ceramic material having excellent plasma resistance can be used. For example, as the materials of the coating films **61**, **62**, and **63**, a dilute earth oxide such as yttrium aluminum garnet (YAG) or yttria (Y_2O_3) or fluoride can be suitably used. The materials of the coating films **61**, **62**, and **63** may be different from each other or may be the same type of material.

[0070] The coating film **61** is formed in close contact with the roughened surface **55**, for example. The coating film **61** is formed to cover the roughened surface **55**. The coating film **61** is formed, for example, so as to cover the entire roughened surface **55**. The coating film **61** is formed, for example, so as to fill unevenness of the roughened surface **55**. The coating film **61** is formed, for example, so as to fill the recesses **56** of the roughened surface **55**. The coating film **61** has higher plasma resistance than the bottom plate portion **51**, for example. For example, the coating film **61** has higher plasma resistance than the coating film **62**. For example, the coating film **61** has a higher density than the coating film **62**. In other words, the coating film **61** is formed denser than the coating film **62**. Here, the density refers to volumetric density (e.g., gram per cubic centimeter). The coating film **61** is thinner than the coating film **62**, for example. A thickness of the coating film **61** may be, for example, about 3 μm to 15 μm. The coating film **61** is, for example, a PVD film formed by physical vapor deposition (PVD). The coating film **61** according to the present embodiment is an yttria film formed by a PVD method.

[0071] The coating film **62** is formed in close contact with the upper surface of the coating film **61**. The coating film **62** is formed to cover the entire upper surface of the coating film **61**. The coating film **62** has higher plasma resistance than the bottom plate portion **51**. For example, the coating film **62** has lower plasma resistance than the coating film **63**. For example, the coating film **62** has a lower density than the coating film **63**. Here, the density refers to volumetric density (e.g., gram per cubic centimeter). The coating film **62** is thicker than the coating film **63**, for example. A thickness of the coating film **62** may be, for example, about 200 μm to 1000 μm. The coating film **62** is, for example, a thermal spray film formed by a thermal spraying method. The coating film **62** according to the present embodiment is an yttria thermally sprayed film formed by the thermal spraying method.

[0072] The coating film **63** is formed in close contact with the upper surface of the coating film **62**. The coating film **63** is formed to cover the entire upper surface of the coating film **62**. The coating film **63** has higher plasma resistance than the bottom plate portion **51**. The coating film **63** has, for example, plasma resistance similar to that of the coating film **61**. For example, the coating film **63** has a density higher than that of the coating film **62**, and has a density similar to that of the coating film **61**. Here, the density refers to volumetric density (e.g., gram per cubic centimeter). The coating film **63** is denser than the coating film **62**. For example, the coating film **63** is thinner than the coating film **62**, and has the same thickness as the coating film **61**. A thickness of the coating film **63** may be, for example, about 3 μm to 15 μm.

[0073] The total thickness of the coating film layer **60**, that is, the total thickness of the coating films **61**, **62**, and **63** is smaller than the thickness of the substrate W, for example. The total thickness of the coating film layer **60** is, for example, 0.5 times or more and less than 1 time the thickness of the substrate W.

[0074] The opening portion **60**X is formed to penetrate the coating film **61**, the coating film **62**, and the coating film **63** in the thickness direction. The inner side surface of the opening portion **60**X is formed, for example, to linearly extend along the thickness direction of the coating film layer **60**, for example. That is, a bottom portion of the opening portion **60**X is not formed in an R shape. A side surface of the coating film **61** constituting the inner side surface of the opening portion **60**X, a side surface of the coating film **62** constituting the inner side surface of the opening portion **60**X, and a side surface of the coating film **63** constituting the inner side surface of the opening portion **60**X are formed, for example, flush with each other. The inner side surface of the opening portion **60**X is in contact with, for example, the side surface of the substrate W accommodated in the opening portion **60**X.

[0075] Method for Manufacturing Substrate Fixing Device **10**

[0076] Next, a method for manufacturing the substrate fixing device **10** will be described. Here, a method for manufacturing the tray **50** will be described in detail.

[0077] In a step illustrated in FIG. **5**, first, the bottom plate portion **51** which is a ceramic substrate is prepared. Subsequently, the recesses **54** are formed in a portion of the upper surface of the bottom plate portion **51** which becomes the substrate placement portion **52**, and the embossed portions **53** are formed in the substrate placement portion **52**. A method for forming the recesses **54** is not particularly limited. The recesses **54** can be formed by, for example, blasting the upper surface of the bottom plate portion **51** while masking the upper surface of the bottom plate portion **51** other than the substrate placement portion **52**.

[0078] Next, a mask member **70** is formed to cover the substrate placement portion **52** on the upper surface of the bottom plate portion **51**. In other words, the mask member **70** is formed to expose only an area of the upper surface of the bottom plate portion **51** where the coating film layer **60** (see FIG. **3**) is to be formed. Thereafter, only a portion of the upper surface of the bottom plate portion **51** exposed from the mask member **70** is roughened. Thus, the upper surface of the bottom plate portion **51** exposed from the mask member **70** is formed as the roughened surface **55**. The roughening treatment can be performed by, for example, etching, blasting, or the like. Although not illustrated, a mask member may be formed to cover a side surface and a lower surface of the bottom plate portion **51**.

[0079] Next, in a step illustrated in FIG. **6**, the coating film **61** is formed on a portion of the upper surface of the bottom plate portion **51** exposed from the mask member **70**. That is, the coating film **61** is formed on the roughened surface **55**. The coating film **61** is formed in close contact with the roughened surface **55**. A side surface of the coating film **61** is formed in contact with side surfaces of the mask members **70**. The coating film **61** can be formed by, for example, a PVD method or a high-speed solid particle deposition method. By forming the coating film **61** by the PVD method or the high-speed solid particle deposition method described above, the coating film **61** can be formed more densely.

[0080] Subsequently, in a step illustrated in FIG. **7**, the coating film **62** is formed on the upper surface of the coating film **61**. The coating film **62** is thicker than the coating film **61**. The coating film **62** can be formed by, for example, the thermal spraying method. The coating film **62** can be formed by, for example, spraying yttria on the upper surface of the coating film **61**. By forming the coating film **62** by such a thermal spraying method, the coating film **62** can be easily formed thick. This step is performed in a state in which the substrate placement portions **52** of the upper surface of the bottom plate portion **51** are covered with the mask members **70**. At this time, the side surface of the coating film **62** is formed in contact with the side surfaces of the mask members **70**.

[0081] Next, in a step illustrated in FIG. **8**, the coating film **63** is formed on the upper surface of the coating film **62**. The coating film **63** can be formed by, for example, the PVD method or the high-speed solid particle deposition method. By forming the coating film **63** by the PVD method or the high-speed solid particle deposition method described above, the coating film **61** can be formed more densely than the coating film **62** which is the thermal spray film. This step is performed in a state in which the substrate placement portions **52** of the upper surface of the bottom plate portion **51** are covered with the mask members **70**. At this time, the side surface of the coating film **63** is formed to be in contact with the side surfaces of the mask members **70**.

[0082] By the above manufacturing steps, the coating film layer **60** including the coating films **61**, **62**, and **63** is formed on the upper surface of the bottom plate portion **51**. Thereafter, the mask members **70** are removed. Thus, the opening portions **60**X of the coating film layer **60** are formed in the portions where the mask members **70** have been formed. Here, the side surfaces of the portions that are in contact with the side surfaces of the mask members **70**, that is, the side surfaces of the coating films **61**, **62**, and **63** that constitute the inner side surfaces of the opening portions **60**X, are formed in a shape along the side surfaces of the mask members **70**. That is, the side surfaces of the coating films **61**, **62**, and **63** constituting the inner side surfaces of the opening portions **60**X are formed to linearly extend along the thickness direction of the coating film layer **60**, for example.

[0083] The tray **50** according to the present embodiment can be manufactured by the above manufacturing steps.

[0084] Next, effects according to the present embodiment will be described.

[0085] (1) The tray **50** includes the bottom plate portion **51** placed on the electrostatic chuck **31**, the coating film layer **60** made of a material different from that of the bottom plate portion **51** and formed on the upper surface of the bottom plate portion **51**, and the opening portions **60**X penetrating the coating film layer **60** in the thickness direction.

[0086] According to this configuration, the opening portion **60**X of the coating film layer **60** and the upper surface of the bottom plate portion **51** exposed to the opening portion **60**X constitute the accommodation recess **50**X for accommodating the substrate W. Accordingly, the opening portion **60**X of the coating film layer **60** can be formed to penetrate the coating film layer **60** in the thickness direction. Therefore, compared to the recess **103**X of the tray **103** of the related art, it is possible to suitably prevent the formation of the R shape on the inner side surface of the opening portion **60**X. As a result, it is possible to suitably prevent inclination of the substrate W in the accommodation recess **50**X. In addition, since it is possible to prevent the formation of the R shape on the inner side surface of the opening portion **60**X, it is not necessary to form an opening diameter of the opening portion **60**X (accommodation recess **50**X) to be larger by the R shape. Therefore, it is possible to suitably prevent movement of the substrate W in the accommodation recess **50**X. Accordingly, the substrate W can be suitably fixed in a state of being accommodated in the accommodation recess **50**X.

[0087] (2) The coating film layer **60** has the multilayer structure including the coating film **62** having higher plasma resistance than the bottom plate portion **51** and the coating film **63** laminated on the upper surface of the coating film **62** and having higher plasma resistance than the coating film **62**. The coating film **62** is thicker than the coating film **63**.

[0088] According to this configuration, it is possible to improve the plasma resistance of the coating film layer **60** by the coating film **63** formed on the upper surface of the coating film **62** while ensuring the total thickness of the coating film layer **60** by the coating film **62**. More specifically, the coating film **63** having higher plasma resistance than the bottom plate portion **51** and the coating film **62** is less likely to be eroded in a plasma atmosphere than the bottom plate portion **51** and the coating film **62**. Therefore, erosion of the coating film **62** and the bottom plate portion **51** in the plasma atmosphere can be suitably prevented by the coating film **63**. As a result, the life of the tray **50** and the substrate fixture **30** can be extended.

[0089] (3) When the coating film **63** is etched and thinned due to long-term use, only the coating film **63** may be formed again, and it is not necessary to replace the entire substrate fixture **30**. Therefore, the operation cost of the substrate fixture **30** can be reduced as compared with the tray **103** of the related art.

[0090] (4) The coating film **63** has a higher density than the coating film **62**. Here, the density refers to volumetric density (e.g., gram per cubic centimeter). Accordingly, the

plasma resistance of the coating film **63** can be more suitably improved than the plasma resistance of the coating film **62**. Therefore, erosion of the coating film **62** and the bottom plate portion **51** in the plasma atmosphere can be suitably prevented by the coating film **63**.

[0091] (5) The coating film layer **60** has the coating film **61** formed on the upper surface of the bottom plate portion **51**. The coating film **61** has higher plasma resistance than the coating film **62**. The coating film **62** is laminated on the upper surface of the coating film **61**. The coating film **61** is thinner than the coating film **62**.

[0092] According to this configuration, the coating film **61** that directly covers the upper surface of the bottom plate portion **51** has higher plasma resistance than the coating film **62**. Therefore, erosion of the bottom plate portion **51** in the plasma atmosphere can be suitably prevented by the coating film **61**. As a result, the life of the bottom plate portion **51** can be extended. Consequently, the life of the tray **50** and the substrate fixture **30** can be extended.

[0093] (6) The coating film **62** is the thermal spray film, and the coating film **61** and the coating film **63** are the PVD films. According to this configuration, since the coating film **62** is formed by the thermal spraying method, the coating film **62** can be easily formed thick. In addition, since the coating film **61** and the coating film **63** are formed by the PVD method, the coating film **61** and the coating film **63** can be formed denser than the coating film **62** which is the thermal spray film. Accordingly, the plasma resistance of the coating film **61** and the coating film **63** can be more suitably improved than the plasma resistance of the coating film **62**. As a result, erosion of the bottom plate portion **51** in the plasma atmosphere can be suitably prevented by the coating film **61** and the coating film **63**.

[0094] (7) The upper surface of the bottom plate portion **51** has the roughened surface **55** having a surface roughness larger than that of the lower surface of the bottom plate portion **51**. The coating film layer **60** is formed to cover the roughened surface **55**. According to this configuration, since adhesion strength between the coating film layer **60** and the roughened surface **55** can be improved, it is possible to suitably prevent the peeling of the coating film layer **60** from the bottom plate portion **51**.

OTHER EMBODIMENTS

[0095] The above embodiment can be modified as follows. The embodiment described above and the following modifications can be combined with each other without technical contradiction.

[0096] As illustrated in FIG. **9**, the coating film layer **60** may be formed to cover the upper surface of the bottom plate portion **51** and the side surface of the bottom plate portion **51**. The coating film layer **60** according to the present modification is formed to cover the entire side surface of the bottom plate portion **51**, for example.

[0097] As illustrated in FIG. **10**, in the coating film layer **60** according to the present modification, a portion covering the upper surface of the bottom plate portion **51** and a portion covering the side surface of the bottom plate portion **51** are continuously and integrally formed. In the coating film layer **60** according to the present modification, the portion covering the upper surface of the bottom plate portion **51** and the portion covering the side surface of the bottom plate portion **51** have the same layer structure. That is, the portion of the coating film layer **60** covering the side surface of the bottom plate portion **51** is formed in a multilayer structure including the coating film **61** covering the side surface of the bottom plate portion **51**, the coating film **62** covering the side surface of the coating film **61**, and the coating film **63** covering the side surface of the coating film **62**. Here, in the present modification, the entire side surface of the bottom plate portion **51** is formed as a roughened surface **58**. The roughened surface **58** has a surface roughness larger than that of the lower surface of the bottom plate portion **51**, for example. The roughened surface **58** may have a surface roughness Ra of 800 nm or more, for example. The coating film **61** is formed to cover the roughened surface **58**. The coating film **61** is formed in close contact with the roughened surface **58**. The coating film **61** is formed, for example, so as to fill unevenness of the roughened surface **58**.

[0098] In the tray **50** according to the present modification, a thickness of the portion thereof covering the side surface (that is, the roughened surface **58**) of the bottom plate portion **51** is smaller than a thickness of the portion thereof covering the upper surface (that is, the roughened surface **55**) of the bottom plate portion **51**. More specifically, a thickness of a portion of the coating film **61** covering the roughened surface **58** is smaller than the thickness of a portion of the coating film **61** covering the roughened surface **55**. A thickness of a portion of the coating film **62** covering the roughened surface **58** is smaller than the thickness of a portion of the coating film **62** covering the roughened surface **55**. A thickness of a portion of the coating film **63** covering the roughened surface **58** is smaller than the thickness of a portion of the coating film **63** covering the roughened surface **55**. The thickness of the portion of the coating film **62** covering the roughened surface **58** is larger than the thickness of each of the portions of the coating films **61** and **62** covering the roughened surface **58**.

[0099] According to this configuration, the side surface of the bottom plate portion **51** can be covered with the coating film layer **60** having higher plasma resistance than the bottom plate portion **51**. Accordingly, erosion of the side surface of the bottom plate portion **51** in the plasma atmosphere can be suitably prevented by the coating film layer **60**. As a result, the life of the tray **50** can be extended.

[0100] The side surface of the bottom plate portion **51** is formed as the roughened surface **58**, and the coating film layer **60** is formed to cover the roughened surface **58**. According to this configuration, since the adhesion strength between the coating film layer **60** and the roughened surface **58** can be improved, it is possible to suitably prevent the peeling of the coating film layer **60** from the side surface of the bottom plate portion **51**.

[0101] In the coating film layer **60** according to the present modification, the thickness of the portion thereof covering the side surface of the bottom plate portion **51** is smaller than the thickness of the portion thereof covering the upper surface of the bottom plate portion **51**. Accordingly, it is possible to prevent an increase in the size of the tray **50** in the planar direction due to the provision of the coating film layer **60** on the side surface of the bottom plate portion **51**.

[0102] In the above embodiment, the coating film layer **60** has the multilayer structure in which the coating film **61**, the coating film **62**, and the coating film **63** are laminated in this order, but is not limited thereto. The layer structure can be

appropriately changed as long as the coating film layer **60** may have any multilayer structure including the coating film **62** and the coating film **63**.

[0103] As illustrated in FIGS. **11** and **12**, the coating film layer **60** may be formed in a multilayer structure in which the coating film **62** and the coating film **63** are laminated in this order. That is, the coating film **61** (see FIG. **4**) may be omitted from the coating film layer **60**. In the coating film layer **60** illustrated in FIG. **11**, the coating film **62** is formed to cover the roughened surface **55**, and the coating film **63** is formed to cover the upper surface of the coating film **62**. The coating film **62** according to the present modification is formed in close contact with the roughened surface **55**. In the coating film layer **60** illustrated in FIG. **12**, the coating film **62** is formed to cover the roughened surface **55** and the roughened surface **58**, and the coating film **63** is formed to cover the upper surface and the side surface of the coating film **62**. The coating film **62** according to the present modification is formed in close contact with the roughened surface **55** and is also formed in close contact with the roughened surface **58**.

[0104] In the modification illustrated in FIGS. **10** and **12**, the thickness of the portion of the coating film layer **60** covering the side surface of the bottom plate portion **51** is smaller than the thickness of the portion of the coating film layer **60** covering the upper surface of the bottom plate portion **51**, but the present invention is not limited thereto. For example, the thickness of the portion of the coating film layer **60** covering the side surface of the bottom plate portion **51** may be equal to the thickness of the portion of the coating film layer **60** covering the upper surface of the bottom plate portion **51**.

[0105] In the modification illustrated in FIGS. **10** and **12**, the layer structure of the coating film layer **60** in the portion covering the upper surface of the bottom plate portion **51** and the layer structure of the coating film layer **60** in the portion covering the side surface of the bottom plate portion **51** are formed in the same layer structure, but the present invention is not limited thereto. For example, the layer structure of the coating film layer **60** in the portion covering the upper surface of the bottom plate portion **51** and the layer structure of the coating film layer **60** in the portion covering the side surface of the bottom plate portion **51** may be formed in different layer structures. For example, the layer structure of the coating film layer **60** in the portion covering the upper surface of the bottom plate portion **51** may be formed into a three-layer structure of the coating films **61**, **62**, and **63**, and the layer structure of the coating film layer **60** in the portion covering the side surface of the bottom plate portion **51** may be formed into a two-layer structure of the coating films **62** and **63**.

[0106] In the above embodiment, the tray **50** is configured to accommodate three substrates W. That is, the tray **50** has three accommodation recesses **50**X that respectively accommodate the three substrates W. However, the number of accommodation recesses **50**X of the tray **50** is not particularly limited. For example, the number of the accommodation recesses **50**X of the tray **50** may be one or two, or four or more.

[0107] For example, as illustrated in FIG. **13**, the tray **50** of the substrate fixture **30** may have seven accommodation recesses **50**X. The substrate fixture **30** in this case can simultaneously accommodate and fix the seven substrates W.

[0108] A planar shape of the accommodation recess **50**X of the tray **50** in the above embodiment is not particularly limited. The planar shape of the accommodation recess **50**X is formed in the same shape as the planar shape of the substrate W accommodated in the accommodation recess **50**X.

[0109] For example, as illustrated in FIG. **14**, when the planar shape of the substrate W is a perfect circular shape having no orientation flat OF, the planar shape of the accommodation recess **50**X (opening portion **60**X) of the tray **50** is formed in a perfect circular shape.

[0110] For example, as illustrated in FIG. **15**, when the planar shape of the substrate W is a rectangular, the planar shape of the accommodation recess **50**X (opening portion **60**X) of the tray **50** is formed in a rectangular shape. The substrate fixture **30** according to the present modification can accommodate and fix only one substrate W.

[0111] In the above embodiment and modification, the portions of the surfaces of the bottom plate portion **51** on which the coating film layer **60** is formed are formed as the roughened surfaces **55** and **58**, but the formation of the roughened surfaces **55** and **58** may be omitted. In this case, for example, the coating film layer **60** is formed on the surface of the bottom plate portion **51** which is a smooth surface.

[0112] In the above embodiment, the plurality of embossed portions **53** and the plurality of recesses **54** are formed in the substrate placement portion **52**, but the formation of the embossed portions **53** and the recesses **54** may be omitted.

[0113] In the above embodiment, the total thickness of the coating film layer **60** is smaller than the thickness of the substrate W, but the present invention is not limited thereto. For example, the total thickness of the coating film layer **60** may be equal to the thickness of the substrate W or may be larger than the thickness of the substrate W.

[0114] In the above embodiment, the same mask member **70** is used as the mask member for roughening the upper surface of the bottom plate portion **51** and the mask member for forming the coating film layer **60**, but the present invention is not limited thereto. For example, the mask member for roughening the upper surface of the bottom plate portion **51** may be different from the mask member for forming the coating film layer **60**.

[0115] In the above embodiment, the substrate fixing device **10** is applied to the semiconductor manufacturing device **1** which is a plasma etching device, but a process in which the substrate fixing device **10** is used is not particularly limited. For example, the substrate fixing device **10** may be used in a process such as CVD.

What is claimed is:

1. A tray mounted on an electrostatic chuck, the tray comprising:

- an accommodation recess configured to accommodate a substrate;
- a bottom plate portion placed on the electrostatic chuck;
- a coating film layer made of a material different from the bottom plate portion and formed on an upper surface of the bottom plate portion; and
- an opening portion penetrating the coating film layer in a thickness direction,

wherein the accommodation recess includes an inner side surface of the opening portion and an upper surface of the bottom plate portion exposed from the opening portion,

wherein the coating film layer has a multilayer structure including a first coating film having higher plasma resistance than the bottom plate portion and a second coating film laminated on an upper surface of the first coating film and having higher plasma resistance than the first coating film, and

wherein the first coating film is thicker than the second coating film.

2. The tray according to claim **1**,

wherein the second coating film has a higher density than the first coating film.

3. The tray according to claim **1**,

wherein the first coating film is a thermal spray film, and

wherein the second coating film is a PVD film.

4. The tray according to claim **1**,

wherein the coating film layer further includes a third coating film formed on an upper surface of the bottom plate portion,

wherein the first coating film is laminated on an upper surface of the third coating film,

wherein the third coating film has higher plasma resistance than the first coating film, and

wherein the third coating film is thinner than the first coating film.

5. The tray according to claim **4**,

wherein the third coating film has a higher density than the first coating film, and

wherein the third coating film is a PVD film.

6. The tray according to claim **1**,

wherein the upper surface of the bottom plate portion has a roughened surface having a surface roughness larger than that of a lower surface of the bottom plate portion, and

wherein the coating film layer is formed to cover the roughened surface.

7. The tray according to claim **6**,

wherein the upper surface of the bottom plate portion has a substrate placement portion exposed from the opening portion,

wherein the substrate placement portion includes a plurality of embossed portions and a plurality of first recesses, and

wherein a second recess constituting the roughened surface is shallower than the first recess.

8. The tray according to claim **1**,

wherein the coating film layer is formed to cover a side surface of the bottom plate portion.

9. The tray according to claim **1**,

wherein the coating film layer has a plurality of the opening portions for accommodating a plurality of the substrates, respectively.

10. A substrate fixing device comprising:

a conductive base plate;

an electrostatic chuck fixed to an upper surface of the base plate; and

a tray including an accommodation recess configured to accommodate a substrate and mounted on an upper surface of the electrostatic chuck,

wherein the tray includes

a bottom plate portion placed on the upper surface of the electrostatic chuck,

a coating film layer made of a material different from the bottom plate portion and formed on an upper surface of the bottom plate portion, and

an opening portion penetrating the coating film layer in a thickness direction,

wherein the accommodation recess includes an inner side surface of the opening portion and an upper surface of the bottom plate portion exposed from the opening portion,

wherein the coating film layer has a multilayer structure including a first coating film having higher plasma resistance than the bottom plate portion and a second coating film laminated on an upper surface of the first coating film and having higher plasma resistance than the first coating film, and

wherein the first coating film is thicker than the second coating film.

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